

CompactFlash® Memory Card Product Manual

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- Revision 5—general editorial changes, CF Type II information added, new higher capacities products added, some lower capacities removed, new card reader/writer vendor added.
- Revision 6—added new 256 Mbit technology products, general and editorial changes.
- Revision 7—changes to Translate Sector command (page 73) and Device Control Register Enable bit (page 53)
- Revision 8—removed CF Type II information, added new higher capacity products, removed some lower capacity products, broadened temperature ranges for 3.3V and 5V operation, modified read & write timing specifications.
- Revision 9—manual format and minor technical and editorial changes.
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1. Introduction to the CompactFlash Memory Card

The SanDisk CompactFlash® Memory Card (CF) products provide high capacity solid state flash memory that electrically complies with the Personal Computer Memory Card International Association ATA (PC Card ATA) standard. (In Japan, the applicable standards group is JEIDA.) The CompactFlash Memory Card Series also supports a True IDE Mode that is electrically compatible with an IDE disk drive. CompactFlash Memory Cards provide up to 4 GB of formatted storage capacity in the CF Type I form factor. The original CF form factor card can be used in any system that has a CF slot, and with a Type II PCMCIA adapter can be used in any system that has a PCMCIA Type II or Type III socket.

The CompactFlash Memory Cards use SanDisk Flash memory, which was designed by SanDisk specifically for use in mass storage applications. In addition to the mass storage specific Flash memory chips, the CompactFlash Memory Cards include an on-card intelligent controller that provides a high level interface to the host computer. This interface allows a host computer to issue commands to the memory card to read or write blocks of memory. The host addresses the card in 512 byte sectors. Each sector is protected by a powerful Error Correcting Code (ECC).

The CompactFlash Memory Card on-card intelligent controller manages interface protocols, data storage and retrieval as well as ECC, defect handling and diagnostics, power management and clock control. Once the CompactFlash Memory Card has been configured by the host, it appears to the host as a standard ATA (IDE) disk drive. Additional ATA commands have been provided to enhance system performance.

The host system can support as many cards as there are CompactFlash and PCMCIA Type II or III card slots. The original form factor CompactFlash Memory Cards require a PCMCIA Type II Adapter to be used in a PCMCIA Type II or Type III socket. Figure 1-1 shows a block diagram of the CompactFlash Memory Card.

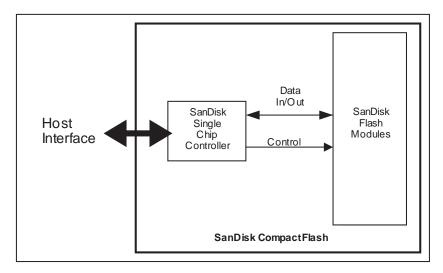


Figure 1-1. CompactFlash Memory Card Block Diagram

1.1. Scope

This document describes the key features and specifications of CompactFlash Memory Cards, as well as the information required to interface this product to a host system. Retail CompactFlash specifications are not covered in this manual.

1.2. System Features

CompactFlash provides the following system features:

- Up to 4.0 GB of mass storage data
- PC Card ATA protocol compatible
- True IDE Mode compatible
- Very low CMOS power
- Very high performance
- · Very rugged
- Low weight
- Noiseless
- Low Profile
- +5 Volts or +3.3 Volts operation
- Automatic error correction and retry capabilities
- Supports power down commands and sleep modes
- Non-volatile storage (no battery required)
- MTBF >1,000,000 hours
- Minimum 10,000 insertions

1.3. PCMCIA Standard

CompactFlash Memory Cards are fully electrically compatible with the PCMCIA specifications listed below:

- PCMCIA PC Card Standard, 7.0, February 1999
- PCMCIA PC Card ATA Specification, 7.0, February 1999

These specifications may be obtained from:

PCMCIA 2635 North First St., Ste. 209 San Jose, CA 95131 USA

Phone: 408-433-2273 FAX: 408-433-9558

1.4. CompactFlash Specification

CompactFlash Memory Cards are fully compatible with the CompactFlash Specification published by the CompactFlash Association. Contact the CompactFlash Association for more information.

CompactFlash Association P.O. Box 51537 Palo Alto, CA 94303 USA Phone: 415-843-1220

FAX: 415-493-1871 www.compactflash.org

1.5. Related Documentation

ATA operation is governed by the ATA-2 specification published by ANSI. You may wish to consult the following document:

American National Standard X3.221: AT Attachment for Interface for Disk Drives Document

Documentation can be ordered from Global Engineering Documents by calling:

1-800-854-7179

1.6. Functional Description

CompactFlash Memory Cards contain a high level, intelligent subsystem as shown in the block diagram, Figure 1-1. This intelligent (microprocessor) subsystem provides many capabilities not found in other types of memory cards. These capabilities include the following:

- Standard ATA register and command set (same as found on most magnetic disk drives).
- Host independence from details of erasing and programming flash memory.
- Sophisticated system for managing defects (analogous to systems found in magnetic disk drives).
- Sophisticated system for error recovery including a powerful error correction code (ECC).
- Power management for low power operation.

1.6.1. Technology Independence

The 512-byte sector size of the CompactFlash Memory Card is the same as that in an IDE magnetic disk drive. To write or read a sector (or multiple sectors), the host computer software simply issues a Read or Write command to the CompactFlash Memory Card. This command contains the address and the number of sectors to write/read. The host software then waits for the command to complete. The host software does not get involved in the details of how the flash memory is erased, programmed or read. This is extremely important as flash devices are expected to get more and more complex in the future. Since the CompactFlash Memory Card Series uses an intelligent on-board controller, the host system software will not require changing as new flash memory evolves. In other words, systems that support the CompactFlash Memory Card today will be able to access future SanDisk cards built with new flash technology without having to update or change host software.

1.6.2. Defect and Error Management

CompactFlash Memory Cards contain a sophisticated defect and error management system. This system is analogous to the systems found in magnetic disk drives and in many cases offers enhancements. If necessary, CompactFlash Memory Cards will rewrite data from a defective sector to a good sector. This is completely transparent to the host and does not consume any user data space.

The CompactFlash Memory Card soft error rate specification is much better than the magnetic disk drive specification. In the extremely rare case a read error does occur, CompactFlash Memory Cards have innovative algorithms to recover the data.

These defect and error management systems, coupled with the solid state construction, give CompactFlash Memory Cards unparalleled reliability.

1.6.3. Wear Leveling

Wear Leveling is an intrinsic part of the Erase Pooling functionality of SanDisk CF using NAND memory. The CF Wear Level command is supported as a NOP operation to maintain backward compatibility with existing software utilities.

1.6.4. Using the Erase Sector and Write without Erase Commands

CompactFlash Memory Cards support the CF ERASE SECTOR and WRITE WITHOUT ERASE commands. In some applications, write operations may be faster if the addresses being written are first erased with the ERASE SECTOR command. WRITE WITHOUT ERASE behaves as a normal write command and no performance gain results from its use.

1.6.5. Automatic Sleep Mode

A unique feature of the SanDisk CompactFlash Memory Card (and other SanDisk products) is automatic entrance and exit from sleep mode. Upon completion of a command, the CompactFlash Card will enter sleep mode to conserve power if no further commands are received within 5 msec. The host does not have to take any action for this to occur. In most systems, the CompactFlash Memory Card is in sleep mode except when the host is accessing it, thus conserving power. Note that the delay from command completion to entering sleep mode can be adjusted.

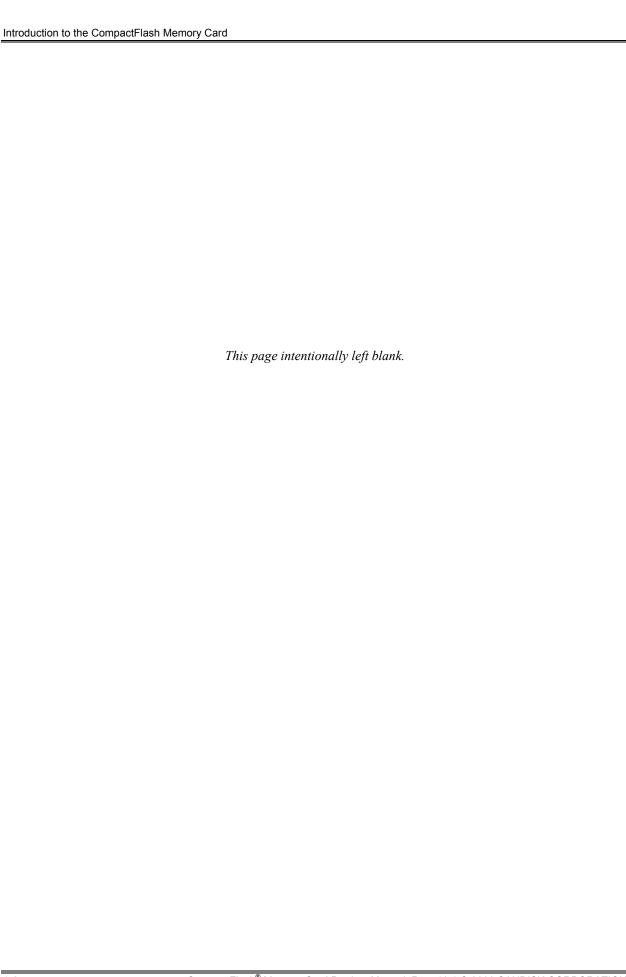
When the host is ready to access the CompactFlash Memory Card and it is in sleep mode, any command issued to the CompactFlash Card will cause it to exit sleep and respond. The host does not have to follow the ATA protocol of issuing a reset first. It may do this if desired, but it is not needed. By not issuing the reset, performance is improved through the reduction of overhead but this must be done only for the SanDisk products as other ATA products may not support this feature.

1.6.6. Dynamic Adjustment of Performance versus Power Consumption

This feature is no longer supported. This command will be treated as a NOP (No Operation) to guarantee backward compatibility.

1.6.7. Power Supply Requirements

This is a dual voltage product, which means it will operate at a voltage range of $3.30 \text{ volts} \pm 5\%$ or $5.00 \text{ volts} \pm 10\%$. Per the PCMCIA specification Section 2.1.1, the host system must apply 0 volts in order to change a voltage range. This same procedure of providing 0 volts to the card is required if the host system applies an input voltage outside the desired voltage by more than 20%. This means less than 4.0 volts for the 5.00 volt range and less than 2.70 volts for the 3.30 volt range.



2. Product Specifications

For all the following specifications, values are defined at ambient temperature and nominal supply voltage unless otherwise stated.

2.1. System Environmental Specifications

Table 2-1. Environmental Specifications

		_
Temperature	Operating: Non-Operating:	0° C to 70° C -25° C to 85° C
Humidity	Operating: Non-Operating:	8% to 95%, non-condensing 8% to 95%, non-condensing
Acoustic Noise		0 dB
Vibration	Operating: Non-Operating:	15 G peak to peak maximum 15 G peak to peak max
Shock	Operating: Non-Operating:	2,000 G maximum 2,000 G maximum
Altitude (relative to sea level)	Operating: Non-Operating:	80,000 feet maximum 80,000 feet maximum

2.2. System Power Requirements

Table 2-2. Power Requirements

DC Input Voltage 100 mV max. ripp	` '	3.3V ±5%	5V ± 10%
(Maximum Average Value) See Notes.	Sleep: Reading: Writing: Read/Write Peak:	350 µA 40 mA 45 mA 100 mA	500 µA 40 mA 65 mA 100 mA

NOTES: All values quoted are typical at ambient temperature and nominal supply voltage unless otherwise stated.

Sleep mode currently is specified under the condition that all card inputs are static CMOS levels and in a "Not Busy" operating state.

The currents specified show the bounds of programmability of the product.

2.3. System Performance

All performance timings assume the CompactFlash Memory Card Series controller is in the default (i.e., fastest) mode.

Table 2-3. Performance

Start Up Times	Sleep to write: Sleep to read: Reset to ready:	2.5 msec maximum 50 msec maximum 50 msec typical 400 msec maximum
Active to Sleep Delay		Programmable
Data Transfer Rate To/From Flash		20.0 MBytes/sec burst
Data Transfer Rate To/From Host		16.0 MBytes/sec burst
Controller Overhead	Command to DRQ	50 msec maximum

NOTE: The Sleep to Write and Sleep to Read times are the times it takes the CompactFlash Memory Card to exit sleep mode when any command is issued by the host to when the card is reading or writing. CompactFlash Memory Cards do not require a reset to exit sleep mode (see Section 1.7.5).

2.4. System Reliability

Table 2-4. Reliability

MTBF (@ 25°C)	>1,000,000 hours
Preventive Maintenance	None
Data Reliability	<1 non-recoverable error in 10 ¹⁴ bits read <1 erroneous correction in 10 ²⁰ bits read

2.5. Physical Specifications

Refer to Table 2-5 and see Figure 2-1 for CompactFlash Memory Card physical specifications and dimensions.

Table 2-5. Physical Specifications

	CompactFlash
Weight:	11.4 g (.40 oz) typical, 14.2 g (.50 oz) maximum
Length:	36.40 ± 0.15 mm (1.433 ±.006 in)
Width:	42.80 ± 0.10 mm (1.685 ±.004 in)
Thickness:	3.3 mm ± 0.10 mm (.130 ±.004 in) (Excluding Lip)

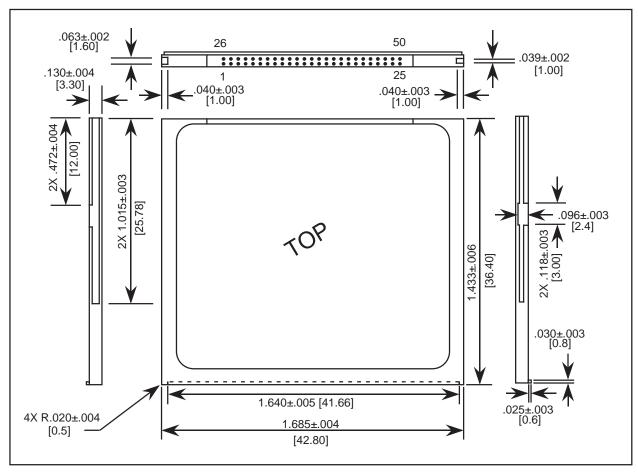


Figure 2-1. CompactFlash Memory Card Dimensions

2.6. Capacity Specifications

Table 2-6 shows the specific capacity for the various models and the default number of heads, sectors/track and cylinders.

Capacity (formatted) Sectors/Card No. of No. of No. of Capacity in bytes (Max LBA+1) Heads Sectors/Track Cylinders 2 8 MB 8,028,160 15,680 32 245 16 MB 16,056,320 31,360 2 32 490 32 MB 32,112,640 62,720 4 32 490 64 MB 64,225,280 125,440 8 32 490 128 MB 128,450,560 250,880 8 32 980 256 MB 256,901,120 501,760 16 32 980 512 MB 993 512,483,328 1,000,944 16 63 1024 MB 1,024,966,656 2,001,888 16 63 1,986 2048 MB 2,048,901,120 4,001,760 16 63 3,970 4096 MB 4,097,802,240 8,003,520 16 63 7,964

Table 2-6. Model Capacities



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3. CompactFlash Memory Card Interface Description

3.1. Physical Description

The host is connected to the CompactFlash Memory Card using a standard 50-pin connector consisting of two rows of 25 female contacts each on 50 mil (1.27 mm) centers.

3.1.1. Pin Assignments and Pin Type

The signal/pin assignments are listed in Table 3-1. Low active signals have a "-" prefix. Pin types are Input, Output or Input/Output. Sections 3.3.1 to 3.3.4 define the DC characteristics for all input and output type structures.

Table 3-1. Pin Assignments and Pin Type

	PC Card Memory Mode				PC Card I	/O Mode			True IDE	Mode	
Pin Num	Signal Name	Pin Type	In, Out ⁴ Type	Pin Num	Signal Name	Pin Type	In, Out ⁴ Type	Pin Num	Signal Name	Pin Type	In, Out ⁴ Type
1	GND		Ground	1	GND		Ground	1	GND		Ground
2	D03	I/O	I1Z,OZ3	2	D03	I/O	I1Z,OZ3	2	D03	I/O	I1Z,OZ3
3	D04	I/O	I1Z,OZ3	3	D04	I/O	I1Z,OZ3	3	D04	I/O	I1Z,OZ3
4	D05	I/O	I1Z,OZ3	4	D05	I/O	I1Z,OZ3	4	D05	I/O	I1Z,OZ3
5	D06	I/O	I1Z,OZ3	5	D06	I/O	I1Z,OZ3	5	D06	I/O	I1Z,OZ3
6	D07	I/O	I1Z,OZ3	6	D07	I/O	I1Z,OZ3	6	D07	I/O	I1Z,OZ3
7	-CE1	I	I3U	7	-CE1	I	I3U	7	-CS0	I	I3Z
8	A10	ı	I1Z	8	A10	ı	I1Z	8	A10 ²	I	I1Z
9	-OE	ı	I3U	9	-OE		I3U	9	-ATA SEL	Ι	I3U
10	A09	I	I1Z	10	A09	-	I1Z	10	A09 ²	Ι	I1Z
11	A08	ı	I1Z	11	A08		I1Z	11	A08 ²	Ι	I1Z
12	A07	I	I1Z	12	A07	-	I1Z	12	A07 ²	Ι	I1Z
13	VCC		Power	13	VCC		Power	13	VCC		Power
14	A06	I	I1Z	14	A06	I	I1Z	14	A06 ²	1	I1Z
15	A05	I	I1Z	15	A05	I	I1Z	15	A05 ²	I	I1Z
16	A04	I	I1Z	16	A04	I	I1Z	16	A04 ²	I	I1Z
17	A03	I	I1Z	17	A03	I	I1Z	17	A03 ²	I	I1Z
18	A02	I	I1Z	18	A02	I	I1Z	18	A02	I	I1Z
19	A01	I	I1Z	19	A01	I	I1Z	19	A01	I	I1Z
20	A00	I	I1Z	20	A00	1	I1Z	20	A00	I	I1Z
21	D00	I/O	I1Z,OZ3	21	D00	I/O	I1Z,OZ3	21	D00	I/O	I1Z,OZ3
22	D01	I/O	I1Z,OZ3	22	D01	I/O	I1Z,OZ3	22	D01	I/O	I1Z,OZ3
23	D02	I/O	I1Z,OZ3	23	D02	I/O	I1Z,OZ3	23	D02	I/O	I1Z,OZ3
24	WP	0	OT3	24	-IOIS16	0	OT3	24	-IOCS16	0	ON3

	PC Card Memory Mode			Card Memory Mode PC Card I/O Mode					True IDE	Mode	
Pin Num	Signal Name	Pin Type	In, Out ⁴ Type	Pin Num	Signal Name	Pin Type	In, Out ⁴ Type	Pin Num	Signal Name	Pin Type	In, Out ⁴ Type
25	-CD2	0	Ground	25	-CD2	0	Ground	25	-CD2	0	Ground
26	-CD1	0	Ground	26	-CD1	0	Ground	26	-CD1	0	Ground
27	D11 ¹	I/O	I1Z,OZ3	27	D11 ¹	I/O	I1Z,OZ3	27	D11 ¹	I/O	I1Z,OZ3
28	D12 ¹	I/O	I1Z,OZ3	28	D12 ¹	I/O	I1Z,OZ3	28	D12 ¹	I/O	I1Z,OZ3
29	D13 ¹	I/O	I1Z,OZ3	29	D13 ¹	1/0	I1Z,OZ3	29	D13 ¹	I/O	I1Z,OZ3
30	D14 ¹	I/O	I1Z,OZ3	30	D14 ¹	1/0	I1Z,OZ3	30	D14 ¹	I/O	I1Z,OZ3
31	D15 ¹	I/O	I1Z,OZ3	31	D15 ¹	I/O	I1Z,OZ3	31	D15 ¹	I/O	I1Z,OZ3
32	-CE21	1	I3U	32	-CE2 ¹		I3U	32	-CS1 ¹	-	I3Z
33	-VS1	0	Ground	33	-VS1	0	Ground	33	-VS1	0	Ground
34	-IORD	1	I3U	34	-IORD		I3U	34	-IORD	-	I3Z
35	-IOWR	1	I3U	35	-IOWR	I	I3U	35	-IOWR	I	I3Z
36	-WE	-	I3U	36	-WE	I	I3U	36	-WE ³	I	I3U
37	RDY/BSY	0	OT1	37	IREQ	0	OT1	37	INTRQ	0	OZ1
38	VCC		Power	38	VCC		Power	38	VCC		Power
39	-CSEL	I	I2Z	39	-CSEL	I	I2Z	39	-CSEL	I	I2U
40	-VS2	0	OPEN	40	-VS2	0	OPEN	40	-VS2	0	OPEN
41	RESET	I	I2Z	41	RESET	I	I2Z	41	-RESET	I	I2Z
42	-WAIT	0	OT1	42	-WAIT	0	OT1	42	IORDY	0	ON1
43	-INPACK	0	OT1	43	-INPACK	0	OT1	43	-INPACK	0	OZ1
44	-REG	I	I3U	44	-REG	I	I3U	44	-REG ³	I	I3U
45	BVD2	I/O	I1U,OT1	45	-SPKR	I/O	I1U,OT1	45	-DASP	I/O	I1U,ON1
46	BVD1	I/O	I1U,OT1	46	-STSCHG	I/O	I1U,OT1	46	-PDIAG	I/O	I1U,ON1
47	D08 ¹	I/O	I1Z,OZ3	47	D08 ¹	I/O	I1Z,OZ3	47	D08 ¹	I/O	I1Z,OZ3
48	D09 ¹	I/O	I1Z,OZ3	48	D09 ¹	I/O	I1Z,OZ3	48	D09 ¹	I/O	I1Z,OZ3
49	D10 ¹	I/O	I1Z,OZ3	49	D10 ¹	I/O	I1Z,OZ3	49	D10 ¹	I/O	I1Z,OZ3
50	GND		Ground	50	GND		Ground	50	GND	- F 1.	Ground

NOTE: 1. These signals are required only for 16-bit access and not required when installed in 8-bit systems. For lowest power dissipation, leave these signals open.
2. Should be grounded by the host.
3. Should be tied to VCC by the host.

^{4.} Please refer to Section 3.3 for definitions of In, Out type.

3.2. Electrical Description

The CompactFlash Memory Card Series is optimized for operation with hosts, which support the PCMCIA I/O interface standard conforming to the PC Card ATA specification. However, the CompactFlash Card may also be configured to operate in systems that support only the memory interface standard. The configuration of the CompactFlash Card will be controlled using the standard PCMCIA configuration registers starting at address 200h in the Attribute Memory space of the CompactFlash Memory Card.

Table 3-2 describes the I/O signals. Signals whose source is the host are designated as inputs while signals that the CompactFlash Memory Card sources are outputs. The CompactFlash Card logic levels conform to those specified in the *PCMCIA Release 2.1 Specification*. See Section 3.3 for definitions of Input and Output type.

Table 3-2. Signal Description

Signal Name	Dir.	Pin	Description
A10—A0 (PC Card Memory Mode)	I	8, 10, 11, 12, 14, 15, 16, 17, 18, 19, 20	These address lines along with the -REG signal are used to select the following: The I/O port address registers within the CompactFlash Card, the memory mapped port address registers within the card, a byte in the card's information structure and its configuration control and status registers.
A10—A0 (PC Card I/O Mode)			This signal is the same as the PC Card Memory Mode signal.
A2—A0 (True IDE Mode) A10—A3 (True IDE Mode)	ı	18, 19, 20	In True IDE Mode only A[2:0] is used to select the one of eight registers in the Task File. In True IDE Mode these remaining address lines should be grounded by the host.
BVD1 (PC Card Memory Mode)	I/O	46	This signal is asserted high as the BVD1 signal since a battery is not used with this product.
-STSCHG (PC Card I/O Mode) Status Changed	•		This signal is asserted low to alert the host to changes in the RDY/-BSY and Write Protect states, while the I/O interface is configured. Its use is controlled by the Card Config and Status Register.
-PDIAG (True IDE Mode)			In the True IDE Mode, this input/output is the Pass Diagnostic signal in the Master/Slave handshake protocol.
BVD2 (PC Card Memory Mode)	I/O	45	This output line is always driven to a high state in Memory Mode since a battery is not required for this product.
-SPKR (PC Card I/O Mode)			This output line is always driven to a high state in I/O Mode since this product does not support the audio function.
-DASP (True IDE Mode)			In the True IDE Mode, this input/output is the Disk Active/Slave Present signal in the Master/Slave handshake protocol.
-CD1, -CD2 (PC Card Memory Mode)	0	26, 25	These Card Detect pins are connected to ground on the CompactFlash Card. They are used by the host to determine if the card is fully inserted into its socket.
-CD1, -CD2 (PC Card I/O Mode)			This signal is the same for all modes.
-CD1, -CD2 (True IDE Mode)			This signal is the same for all modes.

Signal Name	Dir.	Pin	Description
-CE1, -CE2 (PC Card Memory Mode) Card Enable	I	7, 32	These input signals are used both to select the card and to indicate to the card whether a byte or a word operation is being performedCE2 always accesses the odd byte of the wordCE1 accesses the even byte or the Odd byte of the word depending on A0 and -CE2. A multiplexing scheme based on A0, -CE1, -CE2 allows 8 bit hosts to access all data on D0-D7. See Tables 3-11, 3-12, 3-15, and 3-16.
-CE1, -CE2 (PC Card I/O Mode) Card Enable			This signal is the same as the PC Card Memory Mode signal.
-CS0, -CS1 (True IDE Mode)			In the True IDE Mode -CS0 is the chip select for the task file registers while -CS1 is used to select the Alternate Status Register and the Device Control Register.
-CSEL (PC Card Memory Mode)	I	39	This signal is not used for this mode.
-CSEL (PC Card I/O Mode)			This signal is not used for this mode.
-CSEL (True IDE Mode)			This internally pulled up signal is used to configure this device as a Master or a Slave when configured in the True IDE Mode. When this pin is grounded, this device is configured as a Master. When the pin is open, this device is configured as a Slave.
D15—D00 (PC Card Memory Mode)	I/O	31, 30, 29, 28, 27, 49, 48, 47, 6, 5, 4, 3, 2, 23, 22, 21	These lines carry the Data, Commands and Status information between the host and the controller. D00 is the LSB of the Even Byte of the Word. D08 is the LSB of the Odd Byte of the Word.
D15—D00 (PC Card I/O Mode)			These signals are the same as the PC Card Memory Mode signal.
D15—D00 (True IDE Mode)			In True IDE Mode all Task File operations occur in byte mode on the low order bus D00-D07 while all data transfers are 16 bits using D00-D15.
GND (PC Card Memory Mode)		1, 50	Ground.
GND (PC Card I/O Mode)			This signal is the same for all modes.
GND (True IDE Mode)			This signal is the same for all modes.
-INPACK (PC Card Memory Mode)	0	43	This signal is not used in this mode.
-INPACK (PC Card I/O Mode) Input Acknowledge			The Input Acknowledge signal is asserted by the CompactFlash Card when the card is selected and responding to an I/O read cycle at the address that is on the address bus. This signal is used by the host to control the enable of any input data buffers between the card and the CPU.
-INPACK (True IDE Mode)			In True IDE Mode this output signal is not used and should not be connected at the host.
-IORD (PC Card Memory Mode)	Ι	34	This signal is not used in this mode.
-IORD (PC Card I/O Mode)			This is an I/O Read strobe generated by the host. This signal gates I/O data onto the bus from the CompactFlash Card when the card is configured to use the I/O interface.
-IORD (True IDE Mode)			In True IDE Mode, this signal has the same function as in PC Card I/O Mode.

Signal Name	Dir.	Pin	Description
-IOWR (PC Card Memory Mode)	ı	35	This signal is not used in this mode.
-IOWR (PC Card I/O Mode)			The I/O Write strobe pulse is used to clock I/O data on the Card Data bus into the CompactFlash controller registers when the card is configured to use the I/O interface.
			The clocking will occur on the negative to positive edge of the signal (trailing edge).
-IOWR (True IDE Mode)			In True IDE Mode, this signal has the same function as in PC Card I/O Mode.
-OE (PC Card Memory Mode)	I	9	This is an Output Enable strobe generated by the host interface. It is used to read data from the CompactFlash Card in Memory Mode and to read the CIS and configuration registers.
-OE (PC Card I/O Mode)			In PC Card I/O Mode, this signal is used to read the CIS and configuration registers.
-ATA SEL (True IDE Mode)			To enable True IDE Mode this input should be grounded by the host.
RDY/-BSY (PC Card Memory Mode)	0	37	In Memory Mode this signal is set high when the CompactFlash Card is ready to accept a new data transfer operation and held low when the card is busy. The Host memory card socket must provide a pull-up resistor.
			At power up and at Reset, the RDY/-BSY signal is held low (busy) until the CompactFlash Card has completed its power up or reset function. No access of any type should be made to the CompactFlash Card during this time. The RDY/-BSY signal is held high (disabled from being busy) whenever the following condition is true: The CompactFlash Card has been powered up with +RESET continuously disconnected or asserted.
-IREQ (PC Card I/O Mode)			I/O Operation—After the CompactFlash Card has been configured for I/O operation, this signal is used as -Interrupt Request. This line is strobed low to generate a pulse mode interrupt or held low for a level mode interrupt.
INTRQ (True IDE Mode)			In True IDE Mode, this signal is the active high Interrupt Request to the host.
-REG (PC Card Memory Mode) Attribute Memory Select	I	44	This signal is used during Memory Cycles to distinguish between Common Memory and Register (Attribute) Memory accesses. High for Common Memory, Low for Attribute Memory.
-REG (PC Card I/O Mode)			The signal must also be active (low) during I/O Cycles when the I/O address is on the Bus.
-REG (True IDE Mode)			In True IDE Mode this input signal is not used and should be connected to VCC by the host.
RESET (PC Card Memory Mode)	I	41	When the pin is high, this signal resets the CompactFlash Card. The card is Reset only at power up if this pin is left high or open from power-up. The card is also reset when the Soft Reset bit in the Card Configuration Option Register is set.
RESET (PC Card I/O Mode)			This signal is the same as the PC Card Memory Mode signal.
-RESET (True IDE Mode)			In the True IDE Mode this input pin is the active low hardware reset from the host.
VCC (PC Card Memory Mode)		13, 38	+5 V, +3.3 V power.
VCC (PC Card I/O Mode)			This signal is the same for all modes.
VCC (True IDE Mode)			This signal is the same for all modes.

Signal Name	Dir.	Pin	Description
-VS1 -VS2 (PC Card Memory Mode)	0	33 40	Voltage Sense SignalsVS1 is grounded so that the CompactFlash Card CIS can be read at 3.3 volts and -VS2 is open and reserved by PCMCIA for a secondary voltage.
-VS1 -VS2 (PC Card I/O Mode)			This signal is the same for all modes.
-VS1 -VS2 (True IDE Mode)			This signal is the same for all modes.
-WAIT (PC Card Memory Mode)	0	42	SanDisk CompactFlash Memory Cards do not assert the -WAIT signal.
-WAIT (PC Card I/O Mode)			SanDisk CompactFlash Memory Cards do not assert the -WAIT signal.
-IORDY (True IDE Mode)			SanDisk CompactFlash Memory Cards do not assert an -IORDY signal.
-WE (PC Card Memory Mode)	I	36	This is a signal driven by the host and used for strobing memory write data to the registers of the CompactFlash Card when the card is configured in the memory interface mode. It is also used for writing the configuration registers.
-WE (PC Card I/O Mode)			In PC Card I/O Mode, this signal is used for writing the configuration registers.
-WE (True IDE Mode)			In True IDE Mode this input signal is not used and should be connected to VCC by the host.
WP (PC Card Memory Mode) Write Protect	0	24	Memory Mode—The CompactFlash Card does not have a write protect switch. This signal is held low after the completion of the reset initialization sequence.
-IOIS16 (PC Card I/O Mode)			I/O Operation—When the CompactFlash Card is configured for I/O Operation, Pin 24 is used for the -I/O Selected is 16 Bit Port (-IOIS16) function. A Low signal indicates that a 16 bit or odd byte only operation can be performed at the addressed port.
-IOCS16 (True IDE Mode)			In True IDE Mode this output signal is asserted low when this device is expecting a word data transfer cycle.

3.3. Electrical Specification

The following table defines all D.C. Characteristics for the CompactFlash Memory Card Series.

Unless otherwise stated, conditions are:

$$Vcc = 5V \pm 10\%$$

 $Vcc = 3.3V \pm 10\%$
 $Ta = 0^{\circ}C$ to $70^{\circ}C$

Absolute Maximum conditions are:

$$Vcc = -0.3V$$
 min. to 7.0V max.
 $V^* = -0.5V$ min. to $Vcc + 0.5V$ max.

^{*} Voltage on any pin except Vcc with respect to GND.

3.3.1. Input Leakage Control

NOTE: In Table 3-3 x refers to the characteristics described in Section 3.3.2. For example, I1U indicates a pull up resistor with a type 1 input characteristic.

Table 3-3. Input Leakage Control

Туре	Parameter	Symbol	Conditions	MIN	TYP	MAX	Units
IxZ	Input Leakage Current	IL	Vih = Vcc/Vil = Gnd	-1		1	μΑ
IxU	Pull Up Resistor	RPU1	Vcc = 5.0V	50k		500k	Ohm
IxD	Pull Down Resistor	RPD1	Vcc = 5.0V	50k		500k	Ohm

NOTE: The minimum pullup resistor leakage current meets the PCMCIA specification of 10k ohms but is intentionally higher in the CompactFlash Memory Card Series product to reduce power use.

3.3.2. Input Characteristics

Table 3-4. Input Characteristics

Туре	Parameter	Symbol	MIN	TYP	MAX	MIN	TYP	MAX	Units
			VCC = 3.3 V		VCC = 5.0 V				
1	Input Voltage CMOS	Vih Vil	2.4		0.6	2.4		0.8	Volts
2	Input Voltage CMOS	Vih Vil	1.5		0.6	2.0		0.8	Volts
3	Input Voltage CMOS Schmitt Trigger	Vth Vtl		1.8 1.0			2.8 2.0		Volts

3.3.3. Output Drive Type

In Table 3-5 x refers to the characteristics described in Section 3.3.4. For example, OT3 refers to Totempole output with a type 3 output drive characteristic.

Table 3-5. Output Drive Type

Туре	Output Type	Valid Conditions
OTx	Totempole	loh & lol
OZx	Tri-State N-P Channel	loh & lol
OPx	P-Channel Only	loh Only
ONx	N-Channel Only	lol Only

3.3.4. Output Drive Characteristics

Table 3-6. Output Drive Characteristics

Туре	Parameter	Symbol	Conditions	MIN	TYP	MAX	Units
1	Output Voltage	Voh	loh = -4 mA	Vcc -0.8V			Volts
		Vol	IoI = 4 mA			Gnd +0.4V	
2	Output Voltage	Voh	Ioh = -8 mA	Vcc -0.8V			Volts
		Vol	IoI = 8 mA	0.0 V		Gnd +0.4V	
3	Output Voltage	Voh	loh = -8 mA	Vcc -0.8V			Volts
		Vol	IoI = 8 mA	0.07		Gnd +0.4V	
Х	Tri-State Leakage Current	loz	Vol = Gnd Voh = Vcc	-10		10	μA

3.3.5. Power-up/Power-down Timing

The timing specification in Table 3-7 was defined to retain data in the SRAM Card during power-up or power-down cycles and to permit peripheral cards to perform power-up initialization.

Table 3-7 Power-un/Power-down Timing

Item	Symbol	Condition	Value		
			Min	Max	Unit
CE signal level ¹	Vi (CE)	0V <v<sub>CC <2.0V</v<sub>	0	ViMAX	V
		2.0V <v<sub>CC <v<sub>IH</v<sub></v<sub>	<vcc -="" 0.1<="" td=""><td>ViMAX</td><td></td></vcc>	ViMAX	
		<v<sub>IH <v<sub>CC</v<sub></v<sub>	V _{IH}	ViMAX	
CE Setup Time	Tsu (Vcc)		20		ms
CE Setup Time	Tsu (RESET)		20		ms
CE Recover Time	Trec (Vcc)		0.001		ms
V _{CC} Rising Time ²	tpr	10% →90% of (V _{CC} + 5%)	0.1	300	ms
V _{CC} Rising Time ²	tpf	90% of (V _{CC} - 5%) →10%	3.0	300	ms
Reset Width	Tw (RESET)		10		μs
	Th (Hi-z Reset)		1		ms
	Ts (Hi-z Reset)		0		ms

ViMAX means Absolute Maximum Voltage for Input in the period of $0V < V_{CC} < 2.0V$, Vi (CE) is only $0V \sim ViMAX$. The tpr and tpf are defined as "linear waveform" in the period of 10% to 90% or vice-versa. Even if the waveform is not "linear waveform," its rising and falling time must be met by this specification.

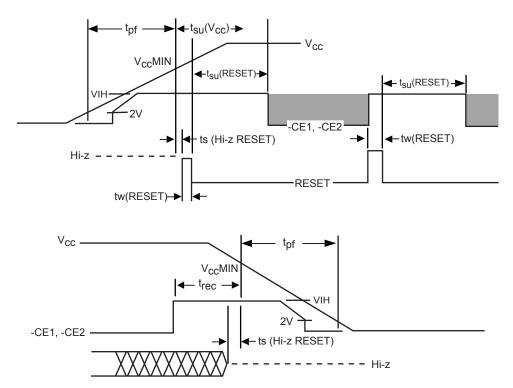


Figure 3-1. Power-Up/Power-Down Timing for Systems Supporting RESET

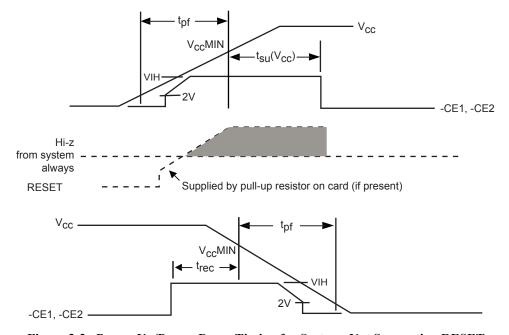


Figure 3-2. Power-Up/Power-Down Timing for Systems Not Supporting RESET

3.3.6. Common Memory Read Timing

Table 3-8. Common Memory Read Timing Specification for all Types of Memory

Speed Version tem	Symbol	IEEE Symbol) ns
			Min	Max
Read Cycle Time	t _c (R)	tAVAV	100	
Address Access Time ¹	t _a (A)	tAVQV		100
Card Enable Access Time	t _a (CE)	tELQV		100
Output Enable Access Time	t _a (OE)	tGLQV		50
Output Disable Time from -OE	t _{dis} (OE)	tGHQZ		50
Output Disable Time from -CE	t _{dis} (CE)	tEHQZ		50
Output Enable Time from -CE	t _{en} (CE)	tELQNZ	5	
Output Enable Time from - OE	t _{en} (OE)	tGLQNZ	5	
Data Valid from Add Change ¹	t _v (A)	tAXQX	0	
Address Setup Time	t _{su} (A)	tAVGL	10	
Address Hold Time	t _h (A)	tGHAX	15	
Card Enable Setup Time	t _{su} (CE)	tELGL	0	
Card Enable Hold Time	t _h (CE)	tGHEH	15	

^{1.} The **-REG** signal timing is identical to address signal timing.

NOTE: All timings measured at the CompactFlash Memory Card. Skews and delays from the system driver/receiver to the CompactFlash Memory Card must be accounted for by the system.

^{2.} SanDisk CompactFlash Memory Cards do not assert the -WAIT Signal.

3.3.7. Common and Attribute Memory Write Timing

The write timing specifications for Common and Attribute memory are the same.

Table 3-9. Common and Attribute Memory Write Timing Specifications

Speed Version Item	Symbol	IEEE	100 ns	
		Symbol		Max
Write Cycle Time	tc(W)	tAVAV	100	
Write Pulse Width	t _w (WE)	tWLWH	60	
Address Setup Time ¹	t _{su} (A)	tAVWL	10	
Address Setup Time for -WE1	t _{su} (A-WEH)	tAVWH	70	
Card Enable Setup Time for -WE	t _{su} (CE-WEH)	tELWH	70	
Data Setup Time from -WE	t _{su} (D-WEH)	tDVWH	40	
Data Hold Time	t _h (D)	tWMDX	15	
Write Recover Time	t _{rec} (WE)	tWMAX	15	
Output Disable Time from -WE	t _{dis} (WE)	tWLQZ		50
Output Disable Time from -OE	t _{dis} (OE)	tGHQZ		50
Output Enable Time from -WE	t _{en} (WE)	tWHQNZ	5	
Output Enable Time from -OE	ten(OE)	tGLQNZ	5	
Output Enable Setup from -WE	t _{su} (OE-WE)	tGHWL	10	
Output Enable Hold from -WE	t _h (OE-WE)	tWHGL	10	
Card Enable Setup Time	t _{su} (CE)	tELWL	0	
Card Enable Hold Time	t _h (CE)	tGHEH	15	

NOTE: All timings measured at the CompactFlash Memory Card. Skews and delays from the system driver/receiver to the CompactFlash Memory Card must be accounted for by the system.

The -REG signal timing is identical to address signal timing.
 SanDisk CompactFlash Memory Cards do not assert the -WAIT signal.

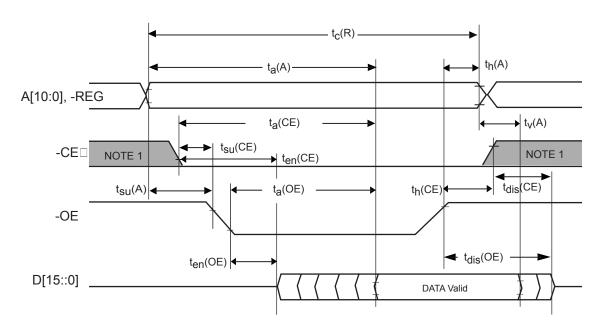
3.3.8. Attribute Memory Read Timing Specification

Table 3-10. Attribute Memory Read Timing Specification for all Types of Memory

Speed Version Item	Symbol	IEEE Symbol	300	300 ns	
			Min	Min	
Read Cycle Time	t _c (R)	tAVAV	300		
Address Access Time	t _a (A)	tAVQV		300	
Card Enable Access Time	t _a (CE)	tELQV		300	
Output Enable Access Time	t _a (OE)	tGLQV		150	
Output Disable Time from -OE	t _{dis} (OE)	tGHQZ		100	
Output Enable Time from - OE	t _{en} (OE)	tGLQNZ	5		
Data Valid from Add Change	t _v (A)	tAXQX	0		
Address Setup Time	t _{su} (A)	tAVGL	30		
Address Hold Time	t _h (A)	tGHAX	20		
Card Enable Setup Time	t _{su} (CE)	tELGL	0		
Card Enable Hold Time	t _h (CE)	tGHEH	20		

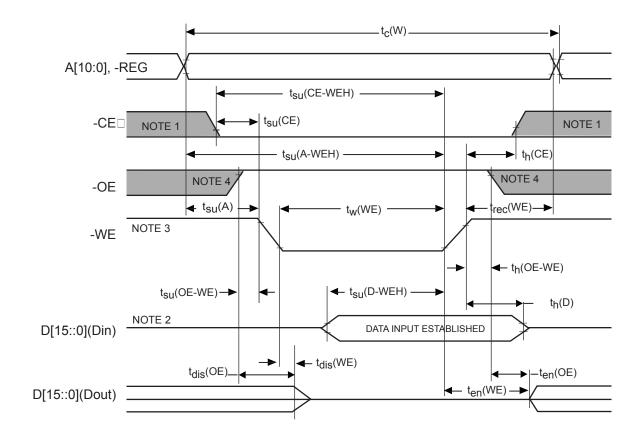
^{1.} SanDisk CompactFlash Memory Cards do not assert the -WAIT signal.

3.3.9. Memory Timing Diagrams



- 1. Shaded areas may be high or low.
- 2. SanDisk CompactFlash Memory Cards do not assert the -WAIT signal.

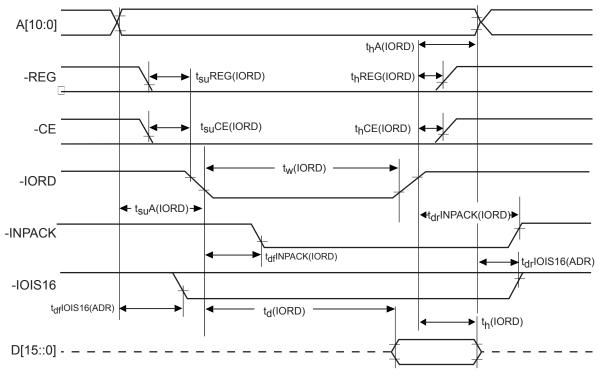
Figure 3-3. Common and Attribute Memory Read Timing Diagram



- 1. Shaded areas may be high or low.
- 2. When the data I/O pins are in the output state, no signals shall be applied to the data pins (D[15::0]) by the host system
- 3. May be high or low for write timing, but restrictions on **-OE** from previous figures apply.
- 4. SanDisk CompactFlash Memory Cards do not assert the **-WAIT** signal.

Figure 3-4. Common and Attribute Memory Write Timing Diagram

3.3.10. I/O Read (Input) Timing Specification



- 1. All timings are measured at the CompactFlash Memory Card.
- Skews and delays from the host system driver/receiver to the CompactFlash Memory Card must be accounted for by the system design.
- 3. **D[15::0]** signifies data provided by the CompactFlash Memory Card to the host system.

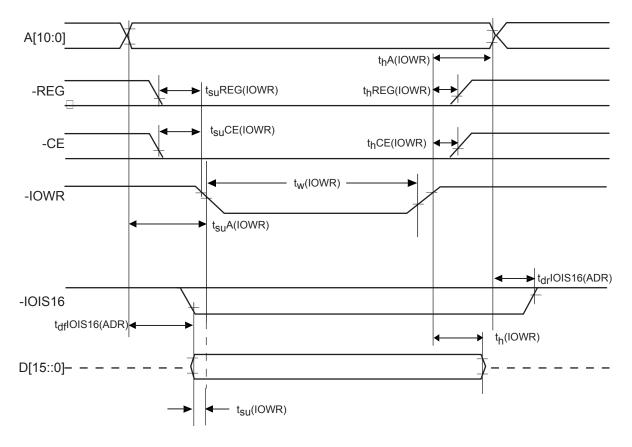
Figure 3-5. I/O Read Timing Diagram

Table 3-11. I/O Read (Input) Timing Specification

Item	Symbol	IEEE Symbol	Min	Max
Data Delay after -IORD	t _d (IORD)	tIGLQV		100
Data Hold following -IORD	t _h (IORD)	tIGHQX	0	
-IORD Width Time	t _w (IORD)	tIGLIGH	165	
Address Setup before -IORD	t _{su} A(IORD)	tAVIGL	70	
Address Hold following -IORD	t _h A(IORD)	tIGHAX	20	
-CE Setup before -IORD	t _{su} CE(IORD)	tELIGL	5	
-CE Hold following -IORD	t _h CE(IORD)	tIGHEH	20	
-REG Setup before -IORD	t _{su} REG(IORD)	tRGLIGL	5	
-REG Hold following -IORD	thREG(IORD)	tIGHRGH	0	
-INPACK Delay Falling from -IORD	t _{df} INPACK(IORD)	tIGLIAL	0	45
-INPACK Delay Rising from -IORD	t _{dr} INPACK(IORD)	tIGHIAH		45
-IOIS16 Delay Falling from Address	t _{df} IOIS16(ADR)	tAVISL		35
-IOIS16 Delay Rising from Address	t _{dr} IOIS16(ADR)	tAVISH		35

- 1. All timings in ns.
- 2. The maximum load on **-INPACK** and **-IOIS16** is 1 LSTTL with 50 pF total load.
- 3. SanDisk CompactFlash Memory Cards do not assert a **-WAIT** Signal.

3.3.11. I/O Write (Output) Timing Specification



- 1. All timings are measured at the CompactFlash Memory Card.
- 2. Skews and delays from the host system driver/receiver to the CompactFlash Memory Card must be accounted for by the system design.
- 3. **D[15::0]** signifies data provided by the host system to the CompactFlash Memory Card.

Figure 3-6. I/O Write Timing Diagram

Table 3-12. I/O Write Timing Specification

Item	Symbol	IEEE Symbol	Min	Max
Data Setup before -IOWR	t _{su} (IOWR)	tDVIWL	60	
Data Hold following -IOWR	t _h (IOWR)	tIWHDX	30	
-IOWR Width Time	t _w (IOWR)	tIWLIWH	165	
Address Setup before -IOWR	t _{su} A(IOWR)	tAVIWL	70	
Address Hold following -IOWR	t _h A(IOWR)	tIWHAX	20	
-CE Setup before -IOWR	t _{su} CE(IOWR)	tELIWL	5	
-CE Hold following -IOWR	t _h CE(IOWR)	tIWHEH	20	
-REG Setup before -IOWR	t _{su} REG(IOWR)	tRGLIWL	5	
-REG Hold following -IOWR	thREG(IOWR)	tIWHRGH	0	
-IOIS16 Delay Falling from Address	t _{df} lOIS16(ADR)	tAVISL		35
-IOIS16 Delay Rising from Address	t _{dr} IOIS16(ADR)	tAVISH		35

^{1.}All timing in ns.

3.3.12. True IDE Mode

The following sections provide valuable information for the True IDE mode.

3.3.12.1. Deskewing

The host shall provide cable deskewing for all signals originating from the device. The device shall provide cable deskewing for all signals originating at the host.

All timing values and diagrams are shown and measured at the connector of the selected device.

3.3.12.2. Transfer Timing

The minimum cycle time supported by devices in PIO mode 3, 4 and Multiword DMA mode 1, 2 respectively shall always be greater than or equal to the minimum cycle time defined by the associated mode, e.g., a device supporting PIO mode 4 timing shall not report a value less than 120 ns. The minimum cycle time defined for PIO mode 4 timings.

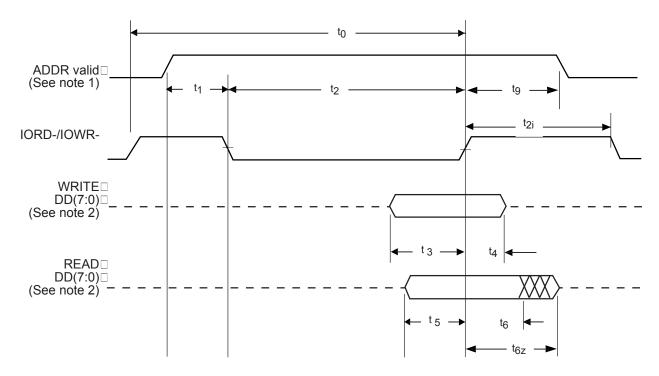
NOTE: PIO Modes greater than 1 are not supported in Industrial Temperature products.

Register Transfers

Figure 3-7 defines the relationships between the interface signals for register transfers.

For PIO modes 3 and above, the minimum value of t_0 is specified by word 68 in the IDENTIFY DEVICE parameter list. Table 3-9 defines the minimum value that shall be placed in word 68.

^{2.} The maximum load on **-IOIS16** is 1 LSTTL with 50 pF total load.



- 1. Device address consists of signals -CS0, -CS1 and -DA(2:0).
- 2. Data consists of DD(7:0).
- 3. SanDisk CompactFlash Memory Cards do not assert an **-IORDY** signal.
- 4. All signals are shown with the asserted condition facing the top of the page. The negated condition is shown towards the bottom of the page relative to the asserted condition.

Figure 3-7. Register Transfer To/From Device

Table 3-13. Register Transfer To/From Device

	PIO Timing Parameters	Mode 4 ns	Note	
t ₀	Cycle time	(min)	120	1
t ₁	Address valid to IORD-/IOWR- setup	(min)	25	
t ₂	IORD-/IOWR- pulse width 8-bit	(min)	70	1
t _{2i}	IORD-/IOWR- recovery time	(min)	25	1
t ₃	IOWR- data setup	(min)	20	
t ₄	IOWR- data hold	(min)	10	
t ₅	IORD- data setup	(min)	20	
t ₆	IORD- data hold	(min)	5	
t _{6z}	IORD- data tri-state	(max)	30	2
t ₉	IORD-/IOWR- to address valid hold	(min)	10	

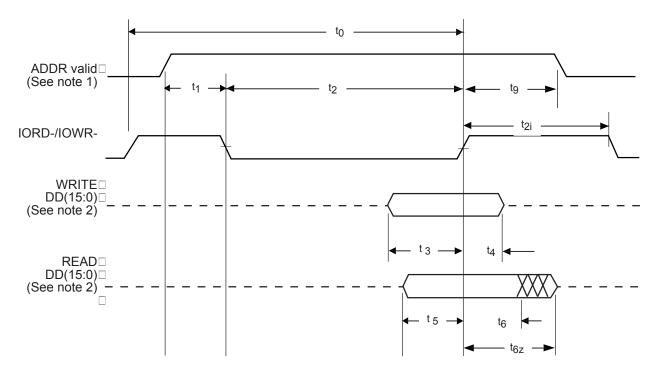
1. t₀ is the minimum total cycle time, t₂ is the minimum command active time, and t_{2i} is the minimum command recovery time or command inactive time. The actual cycle time equals the sum of the actual command active time and the actual command inactive time. The three timing requirements of t₀, t₂, and t_{2i} shall be met. The minimum total cycle time requirements are greater than the sum of t₂ and t_{2i}. This means a host implementation may lengthen either or both t₂ or t_{2i} to ensure that t₀ is equal to or greater than the value reported in the devices IDENTIFY DEVICE data. A device implementation shall support any legal host implementation.

- 2. This parameter specifies the time from the negation edge of /IORD to the time that the data bus is no longer driven by the device (tri-state).
- 3. SanDisk CompactFlash Memory Cards do not assert an -IORDY signal.

PIO Data Transfers

Figure 3-8 defines the relationships between the interface signals for PIO data transfers.

For PIO modes 3 and above, the minimum value of t₀ is specified by word 68 in the IDENTIFY DEVICE parameter list. Table 3-10 defines the minimum value that shall be placed in word 68.



- 1. Device address consists of signals -CS0, -CS1 and -DA(2:0).
- 2. Data consists of DD(15:0).
- 3. SanDisk CompactFlash Memory Cards do not assert an -IORDY signal.
- 4. All signals are shown with the asserted condition facing the top of the page. The negated condition is shown towards the bottom of the page relative to the asserted condition.

Figure 3-8. PIO Data Transfer To/From Device

	PIO Timing Parameters	Mode 0 ns	Mode 1 ns	Mode 2 ns	Mode 3 ns	Mode 4 ns	Note						
t ₀	Cycle time	(min)	600	383	240	180	120	1					
t ₁	Address valid to IORD-/IOWR- setup	(min)	70	50	30	30	25						
t ₂	IORD-/IOWR- pulse width 16-bit	(min)	165	125	100	80	70	1					
t _{2i}	IORD-/IOWR- recovery time	(min)	-	-	-	70	25	1					
t ₃	IOWR- data setup	(min)	60	45	30	30	20						
t ₄	IOWR- data hold	(min)	30	20	15	10	10						
t ₅	IORD- data setup	(min)	50	35	20	20	20						
t ₆	IORD- data hold	(min)	5	5	5	5	5						
t _{6z}	IORD- data tri-state	(max)	30	30	30	30	30	2					
t ₉	IORD-/IOWR- to address valid hold	(min)	20	15	10	10	10						

Table 3-14. PIO Data Transfer To/From Device

- 2. This parameter specifies the time from the negation edge of /IORD to the time that the data bus is no longer driven by the device (tri-state).
- 3. SanDisk CompactFlash Memory Cards do not assert an -IORDY signal.

3.4. Card Configuration

The CompactFlash Memory Cards are identified by appropriate information in the Card Information Structure (CIS). The following configuration registers are used to coordinate the I/O spaces and the Interrupt level of cards that are located in the system. In addition, these registers provide a method for accessing status information about the CompactFlash Card that may be used to arbitrate between multiple interrupt sources on the same interrupt level or to replace status information that appears on dedicated pins in memory cards that have alternate use in I/O cards.

^{1.} t_0 is the minimum total cycle time, t_2 is the minimum command active time, and t_{2i} is the minimum command recovery time or command inactive time. The actual cycle time equals the sum of the actual command active time and the actual command inactive time. The three timing requirements of t_0 , t_2 , and t_{2i} shall be met. The minimum total cycle time requirements are greater than the sum of t_2 and t_{2i} . This means a host implementation may lengthen either or both t_2 or t_{2i} to ensure that t_0 is equal to or greater than the value reported in the devices IDENTIFY DEVICE data. A device implementation shall support any legal host implementation.

Table 3-15. Registers and Memory Space Decoding

250	054	250					sters and		•	•		
-CE2	-CE1	-REG	-OE	-WE	A10	A9	A8-A4	A3	A2	A1	A0	SELECTED SPACE
1	1	Χ	Χ	Χ	Χ	Χ	XX	Χ	Χ	Χ	Χ	Standby
Χ	0	0	0	1	Χ	1	XX	Χ	Χ	Х	0	Configuration Registers Read
1	0	1	0	1	Χ	Χ	XX	Χ	Χ	Х	Χ	Common Memory Read (8 Bit D7-D0)
0	1	1	0	1	Х	Χ	XX	Χ	Χ	Χ	Χ	Common Memory Read (8 Bit D15-D8)
0	0	1	0	1	Х	Χ	XX	Χ	Χ	Х	0	Common Memory Read (16 Bit D15-D0)
Х	0	0	1	0	Х	1	XX	Χ	Χ	Х	0	Configuration Registers Write
1	0	1	1	0	Х	Χ	XX	Χ	Χ	Х	Х	Common Memory Write (8 Bit D7-D0)
0	1	1	1	0	Х	Χ	XX	Χ	Χ	Х	Χ	Common Memory Write (8 Bit D15-D8)
0	0	1	1	0	Х	Χ	XX	Χ	Χ	Х	0	Common Memory Write (16 Bit D15-D0)
Х	0	0	0	1	0	0	XX	Χ	Χ	Х	0	Card Information Structure Read
1	0	0	1	0	0	0	XX	Χ	Χ	Х	0	Invalid Access (CIS Write)
1	0	0	0	1	Х	Χ	XX	Χ	Χ	Х	1	Invalid Access (Odd Attribute Read)
1	0	0	1	0	Х	Χ	XX	Χ	Χ	Х	1	Invalid Access (Odd Attribute Write)
0	1	0	0	1	Х	Χ	XX	Χ	Χ	Х	Х	Invalid Access (Odd Attribute Read)
0	1	0	1	0	Χ	Χ	XX	Χ	Χ	Х	Χ	Invalid Access (Odd Attribute Write)

Table 3-16. Configuration Registers Decoding

-CE2	-CE1	-REG	-OE	-WE	A10	A9	A8-A4	А3	A2	A1	A0	SELECTED REGISTER
Х	0	0	0	1	0	1	00	0	0	0	0	Configuration Option Reg Read
Х	0	0	1	0	0	1	00	0	0	0	0	Configuration Option Reg Write
Х	0	0	0	1	0	1	00	0	0	1	0	Card Status Register Read
Х	0	0	1	0	0	1	00	0	0	1	0	Card Status Register Write
Х	0	0	0	1	0	1	00	0	1	0	0	Pin Replacement Register Read
Х	0	0	1	0	0	1	00	0	1	0	0	Pin Replacement Register Write
Х	0	0	0	1	0	1	00	0	1	1	0	Socket and Copy Register Read
Х	0	0	1	0	0	1	00	0	1	1	0	Socket and Copy Register Write

NOTE: The location of the card configuration registers should always be read from the CIS since these locations may vary in future products. No writes should be performed to the CompactFlash Memory Card attribute memory except to the card configuration register addresses. All other attribute memory locations are reserved.

3.4.1. Attribute Memory Function

Attribute memory is a space where CompactFlash Memory Card identification and configuration information is stored, and is limited to 8-bit wide accesses only at even addresses. The card configuration registers are also located here.

For the Attribute Memory Read function, signals -REG and -OE must be active and -WE inactive during the cycle. As in the Main Memory Read functions, the signals -CE1 and -CE2 control the even-byte and odd-byte address, but only the even-byte data is valid during the Attribute Memory access. Refer to Table 3-12 below for signal states and bus validity for the Attribute Memory function.

Table 3-17. Attribute Memory Function

Function Mode	-REG	-CE2	-CE1	A9	A0	-OE	-WE	D15-D8	D7-D0
Standby Mode	Х	Н	Н	Х	Х	Х	Х	High Z	High Z
Read Byte Access CIS ROM (8 bits)	L	Н	L	L	L	L	Н	High Z	Even Byte
Write Byte Access CIS (8 bits) (Invalid)	L	Н	L	L	L	Н	L	Do not care	Even Byte
Read Byte Access Configuration (8 bits)	L	Н	L	Н	L	L	Н	High Z	Even Byte
Write Byte Access Configuration (8 bits)	L	Н	L	Н	L	Н	L	Do not care	Even Byte
Read Word Access CIS (16 bits)	L	L	L	L	Χ	L	Н	Not Valid	Even Byte
Write Word Access CIS (16 bits) (Invalid)	L	L	L	L	Х	Н	L	Do not care	Even Byte
Read Word Access Configuration (16 bits)	L	L	L	Н	Х	L	Н	Not Valid	Even Byte
Write Word Access Configuration (16 bits)	L	L	L	Н	Х	Н	L	Do not care	Even Byte

NOTE: The -CE signal or both the -OE signal and the -WE signal must be de-asserted between consecutive cycle operations.

3.4.2. Configuration Option Register (Address 200h in Attribute Memory)

The Configuration Option Register is used to configure the cards interface, address decoding and interrupt and to issue a soft reset to the CompactFlash Memory Card.

Operation	D7	D6	D5	D4	D3	D2	D1	D0
R/W	SRESET	LevIREQ	Conf5	Conf4	Conf3	Conf2	Conf1	Conf0

SRESET Soft Reset—Setting this bit to one (1), waiting the minimum reset width time and returning to zero (0)

places the CompactFlash Memory Card in the Reset state. Setting this bit to one (1) is equivalent to assertion of the +RESET signal except that the SRESET bit is not cleared. Returning this bit to zero (0) leaves the CompactFlash Memory Card in the same un-configured, Reset state as following power-up and hardware reset. This bit is set to zero (0) by power-up and hardware reset. Using the PCMCIA Soft Reset is considered a hard Reset by the ATA Commands. Contrast with Soft Reset in the Device Control

Register.

LevIREQ This bit is set to one (1) when Level Mode Interrupt is selected, and zero (0) when Pulse Mode is selected.

Set to zero (0) by Reset.

Conf5—Conf0 Configuration Index. Set to zero (0) by reset. It's used to select operation mode of the CompactFlash

Memory Card as shown below.

NOTE: Conf5 and Conf4 are reserved and must be written as zero (0).

Table 3-18. Card Configurations

Conf5	Conf4	Conf3	Conf2	Conf1	Conf0	Disk Card Mode
0	0	0	0	0	0	Memory Mapped
0	0	0	0	0	1	I/O Mapped, Any 16 byte system decoded boundary
0	0	0	0	1	0	I/O Mapped, 1F0-1F7/3F6-3F7
0	0	0	0	1	1	I/O Mapped, 170-177/376-377

3.4.3. Card Configuration and Status Register (Address 202h in Attribute Memory)

The Card Configuration and Status Register contain information about the Card's condition.

Table 3-19. Card Configuration and Status Register Organization

Operation	D7	D6	D5	D4	D3	D2	D1	D0
Read	Changed	SigChg	IOis8	0	0	PwrDwn	Int	0
Write	0	SigChg	IOis8	0	0	PwrDwn	0	0

Changed Indicates that one or both of the Pin Replacement register CRdy, or CWProt bits are set to one (1). When the

Changed bit is set, -STSCHG Pin 46 is held low if the SigChg bit is a One (1) and the CompactFlash Memory

Card is configured for the I/O interface.

SigChg This bit is set and reset by the host to enable and disable a state-change "signal" from the Status Register, the

Changed bit control pin 46 the Changed Status signal. If no state change signal is desired, this bit should be set to zero (0) and pin 46 (-STSCHG) signal will be held high while the CompactFlash Memory Card is

configured for I/O.

IOis8 The host sets this bit to a one (1) if the CompactFlash Memory Card is to be configured in an 8 bit I/O mode.

The CompactFlash Card is always configured for both 8- and 16-bit I/O, so this bit is ignored.

PwrDwn This bit indicates whether the host requests the CompactFlash Memory Card to be in the power saving or

active mode. When the bit is one (1), the CompactFlash Card enters a power down mode. When zero (0), the host is requesting the CompactFlash Card to enter the active mode. The PCMCIA Rdy/-Bsy value becomes BUSY when this bit is changed. Rdy/-Bsy will not become Ready until the power state requested has been entered. The CompactFlash Card automatically powers down when it is idle and powers back up when it

receives a command.

Int This bit represents the internal state of the interrupt request. This value is available whether or not I/O interface has been configured. This girred requires true until the condition that caused the interrupt request.

interface has been configured. This signal remains true until the condition that caused the interrupt request has been serviced. If interrupts are disabled by the -IEN bit in the Device Control Register, this bit is a zero

(0).

3.4.4. Pin Replacement Register (Address 204h in Attribute Memory)

Table 3-20. Pin Replacement Register

Operation	D7	D6	D5	D4	D3	D2	D1	D0
Read	0	0	CRdy/-Bsy	CWProt	1	1	RRdy/-Bsy	RWProt
Write	0	0	CRdy/-Bsy	CWProt	0	0	MRdy/-Bsy	MWProt

CRdy/-Bsy This bit is set to one (1) when the bit RRdy/-Bsy changes state. This bit can also be written by the host.

CWProt This bit is set to one (1) when the RWprot changes state. This bit may also be written by the host.

RRdy/-Bsy This bit is used to determine the internal state of the Rdy/-Bsy signal. This bit may be used to determine the

state of the Ready/-Busy as this pin has been reallocated for use as Interrupt Request on an I/O card. When

written, this bit acts as a mask for writing the corresponding bit CRdy/-Bsy.

RWProt This bit is always zero (0) since the CompactFlash Memory Card does not have a Write Protect switch. When

written, this bit acts as a mask for writing the corresponding bit CWProt.

MRdy/-Bsy This bit acts as a mask for writing the corresponding bit CRdy/-Bsy.

MWProt This bit when written acts as a mask for writing the corresponding bit CWProt.

Table 3-21. Pin Replacement Changed Bit/Mask Bit Values

Initial Value of	Written	by Host	Final	Comments
(C) Status	"C" Bit "M" Bit		"C" Bit	
0	Х	0	0	Unchanged
1	Х	0	1	Unchanged
Х	0	1	0	Cleared by Host
Х	1	1	1	Set by Host

3.4.5. Socket and Copy Register (Address 206h in Attribute Memory

This register contains additional configuration information. This register is always written by the system before writing the card's Configuration Index Register.

Table 3-22. Socket and Copy Register Organization

Operation	D7	D6	D5	D4	D3	D2	D1	D0
Read	Reserved	0	0	Drive #	0	0	0	0
Write	0	0	0	Drive # (0)	Х	Χ	Χ	Χ

Reserved This bit is reserved for future standardization. This bit must be set to zero (0) by the software when the register is written.

Drive # This bit indicates the drive number of the card if twin card configuration is supported.

X The socket number is ignored by the CompactFlash Memory Card.

3.5. I/O Transfer Function

The following sections provide valuable information for the I/O Transfer function.

3.5.1. I/O Function

The I/O transfer to or from the CompactFlash Memory Card can be either 8 or 16 bits. When a 16-bit accessible port is addressed, the signal -IOIS16 is asserted by the CompactFlash Card. Otherwise, the -IOIS16 signal is de-asserted. When a 16-bit transfer is attempted, and the -IOIS16 signal is not asserted by the CompactFlash Card, the system must generate a pair of 8-bit references to access the word's even byte and odd byte. The CompactFlash Card permits both 8 and 16 bit accesses to all of its I/O addresses, so -IOIS16 is asserted for all addresses to which the CompactFlash Card responds.

Function Code -REG -CE2 -CE1 Α0 -IORD -IOWR D15-D8 D7-D0 Standby Mode Χ Н Н Χ Χ Χ High Z High Z High Z Byte Input Access (8 bits) L Н L L L Н Even-Byte L Н L Н Н High Z Odd-Byte Byte Output Access (8 bits) L Н L L Н L Do not care Even-Byte Н Н Н Do not care Odd-Byte Word Input Access (16 bits) L L L L L Н Odd-Byte Even-Byte L Н Word Output Access (16 bits) L L L L Odd-Byte Even-Byte I/O Read Inhibit Н Χ Χ Χ L Н Do not care Do not care Χ Χ Н I/O Write Inhibit Н Χ L High Z High Z High Byte Input Only (8 bits) L L Н Χ L Н Odd-Byte High Z L L Н Χ Н High Byte Output Only (8 bits) L Odd-Byte Do not care

Table 3-23. I/O Function

3.6. Common Memory Transfer Function

This section contains valuable information on the Common Memory Transfer function.

3.6.1. Common Memory Function

The Common Memory transfer to or from the CompactFlash Memory Card can be either 8 or 16 bits.

The CompactFlash Memory Card permits both 8 and 16 bit accesses to all of its Common Memory addresses.

Function Code -REG -CE2 -CE1 -OE -WE D15-D8 D7-D0 Α0 Standby Mode Χ Н Н Χ Χ Χ High Z High Z Н L Byte Read Access (8 bits) Н L L Н High Z Even-Byte High Z Odd-Byte Η Η L Η L Н Н Н L L Н Byte Write Access (8 bits) L Do not care Even-Byte Do not care Odd-Byte Η Η L Η Η L Н L L Χ L Н Word Read Access (16 bits) Odd-Byte Even-Byte Н L Χ Н Word Write Access (16 bits) L L Odd-Byte Even-Byte Odd Byte Read Only (8 bits) Н L Н Χ L Н Odd-Byte High Z Χ Н ı Odd Byte Write Only (8 bits) Н ı Н Odd-Byte Do not care

Table 3-24. Common Memory Function

3.7. True IDE Mode I/O Transfer Function

This section contains valuable information on the True IDE Mode I/O Transfer function.

3.7.1. True IDE Mode I/O Function

The CompactFlash Memory Card can be configured in a True IDE Mode of operation. This CompactFlash Card is configured in this mode only when the -OE input signal is grounded by the host when power is applied to the card. In this True IDE Mode, the PCMCIA protocol and configuration are disabled and only I/O operations to the Task File and Data Register are allowed. In this mode, no Memory or Attribute Registers are accessible to the host. CompactFlash Cards permit 8 bit data accesses if the user issues a Set Feature Command to put the device in 8-bit Mode.

NOTE: Removing and reinserting the CompactFlash Memory Card while the host computer's power is on will reconfigure the CompactFlash Card to PC Card ATA mode from the original True IDE Mode. To configure the CompactFlash Card in True IDE Mode, the 50-pin socket must be power cycled with the CompactFlash Card inserted and -OE (output enable) grounded by the host.

Table 3-25 defines the function of the operations for the True IDE Mode.

Function Code -CE2 -CE1 A0 -IORD -IOWR D15-D8 D7-D0 L Χ Invalid Mode L Χ Χ High Z High Z Н Χ Χ Χ Standby Mode Н High Z High Z Task File Write Н L 1-7h Н L Do not care Data In Н Task File Read L 1-7h L Н High Z Data Out L L Data Register Write 0 Н Odd-Byte Even-Byte In In ı ı Н 0 Н Odd-Byte Even-Byte Data Register Read Out Out Control Register Write L Н 6h Н L Do not care Control In Alt Status Read Н 6h L Н High Z Status Out

Table 3-25. IDE Mode I/O Function

4. ATA Drive Register Set Definition and Protocol

The CompactFlash Memory Card can be configured as a high performance I/O device through the following ways:

- Standard PC-AT disk I/O address spaces 1F0h-1F7h, 3F6h-3F7h (primary); 170h-177h, 376h-377h (secondary) with IRQ 14 (or other available IRQ).
- Any system decoded 16-byte I/O block using any available IRQ.
- Memory space.

The communication to or from the CompactFlash Memory Card is done using the Task File registers, which provide all the necessary registers for control and status information. The PCMCIA interface connects peripherals to the host using four register mapping methods. Table 4-1 is a detailed description of these methods.

Standard Configurations Config Index IO or Memory Address Drive # Description 0-F, 400-7FF 0 Memory Mapped Memory I/O XX0-XXF 0 I/O Mapped 16 Contiguous Registers 2 I/O 0 1F0-1F7, 3F6-3F7 Primary I/O Mapped Drive 0 2 Primary I/O Mapped Drive 1 I/O 1F0-1F7, 3F6-3F7 1 3 I/O 170-177, 376-377 0 Secondary I/O Mapped Drive 0 3 1/0 170-177, 376-377 1 Secondary I/O Mapped Drive 1

Table 4-1. I/O Configurations

4.1. I/O Primary and Secondary Address Configurations

-REG	A9-A4	А3	A2	A 1	A0	-IORD=0	-IOWR=0	Note
0	1F(17)	0	0	0	0	Even RD Data	Even WR Data	1, 2
0	1F(17)	0	0	0	1	Error Register	Features	1
0	1F(17)	0	0	1	0	Sector Count	Sector Count	
0	1F(17)	0	0	1	1	Sector No.	Sector No.	
0	1F(17)	0	1	0	0	Cylinder Low	Cylinder Low	
0	1F(17)	0	1	0	1	Cylinder High	Cylinder High	
0	1F(17)	0	1	1	0	Select Card/Head	Select Card/Head	
0	1F(17)	0	1	1	1	Status	Command	
0	3F(37)	0	1	1	0	Alt Status	Device Control	
0	3F(37)	0	1	1	1	Drive Address	Reserved	

Table 4-2. Primary and Secondary I/O Decoding

- 1. Register 0 is accessed with -CE1 low and -CE2 low (and A0 = Do not care) as a word register on the combined Odd Data Bus and Even Data Bus (D15-D0). This register may also be accessed by a pair of byte accesses to the offset 0 with -CE1 low and -CE2 high. Note that the address space of this word register overlaps the address space of the Error and Feature byte-wide registers that lie at offset 1. When accessed twice as byte register with -CE1 low, the first byte to be accessed is the even byte of the word and the second byte accessed is the odd byte of the equivalent word access.
- 2. A byte access to register 0 with -CE1 high and -CE2 low accesses the error (read) or feature (write) register.

4.2. Contiguous I/O Mapped Addressing

When the system decodes a contiguous block of I/O registers to select the CompactFlash Memory Card, the registers are accessed in the block of I/O space decoded by the system as follows:

-REG	A3	A2	A 1	A0	Offset	-IORD=0	-IOWR=0	Notes
0	0	0	0	0	0	Even RD Data	Even WR Data	1
0	0	0	0	1	1	Error	Features	2
0	0	0	1	0	2	Sector Count	Sector Count	
0	0	0	1	1	3	Sector No.	Sector No.	
0	0	1	0	0	4	Cylinder Low	Cylinder Low	
0	0	1	0	1	5	Cylinder High	Cylinder High	
0	0	1	1	0	6	Select Card/Head	Select Card/Head	
0	0	1	1	1	7	Status	Command	
0	1	0	0	0	8	Dup Even RD Data	Dup. Even WR Data	2
0	1	0	0	1	9	Dup. Odd RD Data	Dup. Odd WR Data	2
0	1	1	0	1	D	Dup. Error	Dup. Features	2
0	1	1	1	0	E	Alt Status	Device Ctl	
0	1	1	1	1	F	Drive Address	Reserved	

Table 4-3. Contiguous I/O Decoding

NOTES: 1. Register 0 is accessed with -CE1 low and -CE2 low (and A0 = Do not care) as a word register on the combined Odd Data Bus and Even Data Bus (D15-D0). This register may also be accessed by a pair of byte accesses to the offset 0 with -CE1 low and -CE2 high. Note that the address space of this word register overlaps the address space of the Error and Feature byte-wide registers that lie at offset 1. When accessed twice as byte register with -CE1 low, the first byte to be accessed is the even byte of the word and the second byte accessed is the odd byte of the equivalent word access.

A byte access to register 0 with -CE1 high and -CE2 low accesses the error (read) or feature (write) register.

- 2. Registers at offset 8, 9 and D are non-overlapping duplicates of the registers at offset 0 and 1. Register 8 is equivalent to register 0, while register 9 accesses the odd byte. Therefore, if the registers are byte accessed in the order 9 then 8 the data will be transferred odd byte then even byte. Repeated byte accesses to register 8 or 0 will access consecutive (even than odd) bytes from the data buffer. Repeated word accesses to register 8, 9 or 0 will access consecutive words from the data buffer. Repeated byte accesses to register 9 are not supported. However, repeated alternating byte accesses to registers 8 then 9 will access consecutive (even then odd) bytes from the data buffer. Byte accesses to register 9 access only the odd byte of the data.
- 3. Address lines that are not indicated are ignored by the CompactFlash Memory Card for accessing all the registers in this table.

4.3. Memory Mapped Addressing

When the CompactFlash Memory Card registers are accessed via memory references, the registers appear in the common memory space window: 0-2K bytes as shown in Table 4-4.

-REG	A10	A9-A4	A3	A2	A 1	A0	Offset	-OE=0	-WE=0	Notes
1	0	Х	0	0	0	0	0	Even RD Data	Even WR Data	1
1	0	Х	0	0	0	1	1	Error	Features	2
1	0	Х	0	0	1	0	2	Sector Count	Sector Count	
1	0	Х	0	0	1	1	3	Sector No.	Sector No.	
1	0	Х	0	1	0	0	4	Cylinder Low	Cylinder Low	
1	0	Х	0	1	0	1	5	Cylinder High	Cylinder High	
1	0	Х	0	1	1	0	6	Select Card/Head	Select Card/Head	
1	0	Х	0	1	1	1	7	Status	Command	
1	0	Х	1	0	0	0	8	Dup. Even RD Data	Dup. Even WR Data	2
1	0	Х	1	0	0	1	9	Dup. Odd RD Data	Dup. Odd WR Data	2
1	0	Х	1	1	0	1	D	Dup. Error	Dup. Features	2
1	0	Х	1	1	1	0	E	Alt Status	Device Ctl	
1	0	Х	1	1	1	1	F	Drive Address	Reserved	
1	1	Х	Χ	Χ	Χ	0	8	Even RD Data	Even WR Data	3
1	1	Х	Χ	Χ	Χ	1	9	Odd RD Data	Odd WR Data	3

Table 4-4. Memory Mapped Decoding

NOTES: 1. Register 0 is accessed with -CE1 low and -CE2 low as a word register on the combined Odd Data Bus and Even Data Bus (D15-D0). This register may also be accessed by a pair of byte accesses to the offset 0 with -CE1 low and -CE2 high. Note that the address space of this word register overlaps the address space of the Error and Feature byte-wide registers that lie at offset 1. When accessed twice as byte register with -CE1 low, the first byte to be accessed is the even byte of the word and the second byte accessed is the odd byte of the equivalent word access.

A byte access to address 0 with -CE1 high and -CE2 low accesses the error (read) or feature (write) register.

- 2. Registers at offset 8, 9 and D are non-overlapping duplicates of the registers at offset 0 and 1. Register 8 is equivalent to register 0, while register 9 accesses the odd byte. Therefore, if the registers are byte accessed in the order 9 then 8 the data will be transferred odd byte then even byte. Repeated byte accesses to register 8 or 0 will access consecutive (even then odd) bytes from the data buffer. Repeated word accesses to register 8, 9 or 0 will access consecutive words from the data buffer. Repeated byte accesses to register 9 are not supported. However, repeated alternating byte accesses to registers 8 then 9 will access consecutive (even then odd) bytes from the data buffer. Byte accesses to register 9 access only the odd byte of the data.
- 3. Accesses to even addresses between 400h and 7FFh access register 8. Accesses to odd addresses between 400h and 7FFh access register 9. This 1 KByte memory window to the data register is provided so that hosts can perform memory to memory block moves to the data register when the register lies in memory space. Some hosts, such as the X86 processors, must increment both the source and destination addresses when executing the memory to memory block move instruction. Some PCMCIA socket adapters also have auto incrementing address logic embedded within them. This address window allows these hosts and adapters to function efficiently. Note that this entire window accesses the Data Register FIFO and does not allow random access to the data buffer within the CompactFlash Memory Card.

4.4. True IDE Mode Addressing

When the CompactFlash Memory Card is configured in the True IDE Mode the I/O decoding is as listed in Table 4-5.

-CE2	-CE1	A2	A 1	A0	-IORD=0	-IOWR=0
1	0	0	0	0	Even RD Data	Even WR Data
1	0	0	0	1	Error Register	Features
1	0	0	1	0	Sector Count	Sector Count
1	0	0	1	1	Sector No.	Sector No.
1	0	1	0	0	Cylinder Low	Cylinder Low
1	0	1	0	1	Cylinder High	Cylinder High
1	0	1	1	0	Select Card/Head	Select Card/Head
1	0	1	1	1	Status	Command
0	1	1	1	0	Alt Status	Device Control
0	1	1	1	1	Drive Address	Reserved

Table 4-5. True IDE Mode I/O Decoding

4.5. ATA Registers

NOTE: In accordance with the PCMCIA specification: each of the registers below which is located at an odd offset address may be accessed at its normal address and also the corresponding even address (normal address -1) using data bus lines (D15-D8) when -CE1 is high and -CE2 is low unless -IOIS16 is high (not asserted) and an I/O cycle is being performed.

4.5.1. Data Register (Address—1F0[170];Offset 0, 8, 9)

The Data Register is a 16-bit register, and it is used to transfer data blocks between the CompactFlash Memory Card data buffer and the Host. This register overlaps the Error Register. The table below describes the combinations of data register access and is provided to assist in understanding the overlapped Data Register and Error/Feature Register rather than to attempt to define general PCMCIA word and byte access modes and operations. See the PCMCIA PC Card Standard Release 2.0 for definitions of the Card Accessing Modes for I/O and Memory cycles.

NOTE: Because of the overlapped registers, access to the 1F1, 171 or offset 1 are not defined for word (-CE2 = 0 and -CE1 = 0) operations. SanDisk products treat these accesses as accesses to the Word Data Register. The duplicated registers at offsets 8, 9 and Dh have no restrictions on the operations that can be performed by the socket.

Table 4-6. Data Register

Data Register	CE2-	CE1-	Α0	Offset	Data Bus
Word Data Register	0	0	Х	0,8,9	D15-D0
Even Data Register	1	0	0	0,8	D7-D0
Odd Data Register	1	0	1	9	D7-D0
Odd Data Register	0	1	Х	8,9	D15-D8
Error/Feature Register	1	0	1	1, Dh	D7-D0
Error/Feature Register	0	1	Х	1	D15-D8
Error/Feature Register	0	0	Х	Dh	D15-D8

4.5.2. Error Register (Address—1F1[171]; Offset 1, 0Dh Read Only)

This register contains additional information about the source of an error when an error is indicated in bit 0 of the Status register. The bits are defined as follows:

D7	D6	D5	D4	D3	D2	D1	D0
BBK	UNC	0	IDNF	0	ABRT	0	AMNF

This register is also accessed on data bits D15-D8 during a write operation to offset 0 with -CE2 low and -CE1 high.

Bit 7 (BBK) This bit is set when a Bad Block is detected.

Bit 6 (UNC) This bit is set when an Uncorrectable Error is encountered.

Bit 5 This bit is 0.

Bit 4 (IDNF) The requested sector ID is in error or cannot be found.

Bit 3 This bit is 0.

Bit 2 (Abort) This bit is set if the command has been aborted because of a CompactFlash Memory Card status condition:

(Not Ready, Write Fault, etc.) or when an invalid command has been issued.

Bit 1 This bit is 0.

Bit 0 (AMNF) This bit is set in case of a general error.

4.5.3. Feature Register (Address-1F1[171]; Offset 1, 0Dh Write Only

This register provides information regarding features of the CompactFlash Memory Card that the host can utilize. This register is also accessed on data bits D15-D8 during a write operation to Offset 0 with -CE2 low and -CE1 high.

4.5.4. Sector Count Register (Address—1F2[172]; Offset 2)

This register contains the number of sectors of data requested to be transferred on a read or write operation between the host and the CompactFlash Memory Card. If the value in this register is zero, a count of 256 sectors is specified. If the command was successful, this register is zero at command completion. If not successfully completed, the register contains the number of sectors that need to be transferred in order to complete the request.

4.5.5. Sector Number (LBA 7-0) Register (Address—1F3[173]; Offset 3)

This register contains the starting sector number or bits 7-0 of the Logical Block Address (LBA) for any CompactFlash Memory Card data access for the subsequent command.

4.5.6. Cylinder Low (LBA 15-8) Register (Address—1F4[174]; Offset 4)

This register contains the low order 8 bits of the starting cylinder address or bits 15-8 of the Logical Block Address.

4.5.7. Cylinder High (LBA 23-16) Register (Address—1F5[175]; Offset 5)

This register contains the high order bits of the starting cylinder address or bits 23-16 of the Logical Block Address.

4.5.8. Drive/Head (LBA 27-24) Register (Address 1F6[176]; Offset 6)

The Drive/Head register is used to select the drive and head. It is also used to select LBA addressing instead of cylinder/head/sector addressing. The bits are defined as follows:

□ D 7	D6	D5	D4	D3	D2	D1	D0
1	LBA	1	DRV	HS3	HS2	HS1	HS0

Bit 6 LBA is a flag to select either Cylinder/Head/Sector (CHS) or Logical Block Address Mode (LBA). When

LBA=0, Cylinder/Head/Sector mode is selected. When LBA=1, Logical Block Address is selected. In

Logical Block Mode, the Logical Block Address is interpreted as follows:

LBA07-LBA00: Sector Number Register D7-D0. LBA15-LBA08: Cylinder Low Register D7-D0. LBA23-LBA16: Cylinder High Register D7-D0. LBA27-LBA24: Drive/Head Register bits HS3-HS0.

Bit 5 This bit is set to 1.

Bit 4 (DRV) This bit will have the following meaning. DRV is the drive number. When DRV=0, drive (card) 0 is selected

When DRV=1, drive (card) 1 is selected. The CompactFlash Card is set to be Card 0 or 1 using the copy field

of the PCMCIA Socket & Copy configuration register.

Bit 3 (HS3) When operating in the Cylinder, Head, Sector mode, this is bit 3 of the head number. It is Bit 27 in the

Logical Block Address mode.

Bit 2 (HS2) When operating in the Cylinder, Head, Sector mode, this is bit 2 of the head number. It is Bit 26 in the

Logical Block Address mode.

Bit 1 (HS1) When operating in the Cylinder, Head, Sector mode, this is bit 1 of the head number. It is Bit 25 in the

Logical Block Address mode.

Bit 0 (HS0) When operating in the Cylinder, Head, Sector mode, this is bit 0 of the head number. It is Bit 24 in the

Logical Block Address mode.

4.5.9. Status & Alternate Status Registers (Address 1F7[177]&3F6[376]; Offsets 7 & Eh)

These registers return the CompactFlash Memory Card status when read by the host. Reading the Status register does clear a pending interrupt while reading the Auxiliary Status register does not. The meaning of the status bits are described as follows:

□D7	D6	D5	D4	D3	D2	D1	D0
BUSY	RDY	DWF	DSC	DRQ	CORR	0	ERR

Bit 7 (BUSY)	The busy bit is set when the CompactFlash Memory Card has access to the command buffer and registers and the host is locked out from accessing the command register and buffer. No other bits in this register are valid when this bit is set to a 1.
Bit 6 (RDY)	RDY indicates whether the device is capable of performing CompactFlash Memory Card operations. This bit is cleared at power up and remains cleared until the CompactFlash Card is ready to accept a command.
Bit 5 (DWF)	This bit, if set, indicates a write fault has occurred.
Bit 4 (DSC)	This bit is set when the CompactFlash Memory Card is ready.
Bit 3 (DRQ)	The Data Request is set when the CompactFlash Memory Card requires that information be transferred either to or from the host through the Data register.
Bit 2 (CORR)	This bit is set when a Correctable data error has been encountered and the data has been corrected. This condition does not terminate a multi-sector read operation.
Bit 1 (IDX)	This bit is always set to 0.
Bit 0 (ERR)	This bit is set when the previous command has ended in some type of error. The bits in the Error register contain additional information describing the error.

4.5.10. Device Control Register (Address—3F6[376]; Offset Eh)

This register is used to control the CompactFlash Memory Card interrupt request and to issue an ATA soft reset to the card. The bits are defined as follows:

D7	D6	D5	D4	D3	D2	D1	D0
Х	Х	Х	Х	1	SW Rst	-IEn	0

Bit 7	This bit is an X (Do not care).
Bit 6	This bit is an X (Do not care).
Bit 5	This bit is an X (Do not care).
Bit 4	This bit is an X (Do not care).
Bit 3	This bit is ignored by the CompactFlash Memory Card.
Bit 2 (SW Rst)	This bit is set to 1 in order to force the CompactFlash Memory Card to perform an AT Disk controller Soft Reset operation. This does not change the PCMCIA Card Configuration Registers (4.3.2 to 4.3.5) as a hardware Reset does. The Card remains in Reset until this bit is reset to '0'.
Bit 1 (-IEn)	The Interrupt Enable bit enables interrupts when the bit is 0. When the bit is 1, interrupts from the CompactFlash Memory Card are disabled. This bit also controls the Int bit in the Configuration and Status Register. This bit is set to 0 at power on and Reset.
Bit 0	This bit is ignored by the CompactFlash Memory Card.

4.5.11. Card (Drive) Address Register (Address 3F7[377]; Offset Fh)

This register is provided for compatibility with the AT disk drive interface. It is recommended that this register not be mapped into the host's I/O space because of potential conflicts on Bit 7. The bits are defined as follows:

D7	D6	D5	D4	D3	D2	D1	D0
Χ	-WTG	-HS3	-HS2	-HS1	-HS0	-nDS1	-nDS0

Bit 7 This bit is unknown.

Implementation Note:

Conflicts may occur on the host data bus when this bit is provided by a Floppy Disk Controller operating at the same addresses as the CompactFlash Memory Card. Following are some possible solutions to this problem for the PCMCIA implementation:

- 1. Locate the CompactFlash Memory Card at a non-conflicting address, i.e., Secondary address (377) or in an independently decoded Address Space when a Floppy Disk Controller is located at the Primary addresses.
- 2. Do not install a Floppy and a CompactFlash Memory Card in the system at the same time.

- 3. Implement a socket adapter that can be programmed to (conditionally) tri-state D7 of I/O address 3F7/377 when a CompactFlash Memory Card is installed and conversely to tri-state D6-D0 of I/O address 3F7/377 when a floppy controller is installed.
- 4. Do not use the CompactFlash Memory Card's Drive Address register. This may be accomplished by either a) If possible, program the host adapter to enable only I/O addresses 1F0-1F7, 3F6 (or 170-177, 176) to the CompactFlash Memory Card or b) if provided use an additional Primary/Secondary configuration in the CompactFlash Card which does not respond to accesses to I/O locations 3F7 and 377. With either of these implementations, the host software must not attempt to use information in the Drive Address Register.

	implementations, the nost software must not attempt to use informat
Bit 6 (-WTG)	This bit is 0 when a write operation is in progress, otherwise, it is 1.
Bit 5 (-HS3)	This bit is the negation of bit 3 in the Drive/Head register.
Bit 4 (-HS2)	This bit is the negation of bit 2 in the Drive/Head register.
Bit 3 (-HS1)	This bit is the negation of bit 1 in the Drive/Head register.
Bit 2 (-HS0)	This bit is the negation of bit 0 in the Drive/Head register.
Bit 1 (-nDS1)	This bit is 0 when drive 1 is active and selected.
Bit 0 (-nDS0)	This bit is 0 when the drive 0 is active and selected.

5. ATA Command Description

This section defines the software requirements and the format of the commands the host sends to the CompactFlash Memory Cards. Commands are issued to the CompactFlash Card by loading the required registers in the command block with the supplied parameters, and then writing the command code to the Command Register. The manner in which a command is accepted varies. There are three classes (see Table 5-1) of command acceptance, all dependent on the host not issuing commands unless the CompactFlash Card is not busy. (The BUSY bit in the status and alternate status registers is 0.)

- Upon receipt of a Class 1 command, the CompactFlash Card sets the BUSY bit within 400 nsec.
- Upon receipt of a Class 2 command, the CompactFlash Memory Card sets the BUSY bit within 400 nsec, sets up the sector buffer for a write operation, sets DRQ within 700 μsec, and clears the BUSY bit within 400 nsec of setting DRQ.
- Upon receipt of a Class 3 command, the CompactFlash Memory Card sets the BUSY bit within 400 nsec, sets up the sector buffer for a write operation, sets DRQ within 20 msec (assuming no reassignments), and clears the BUSY bit within 400 nsec of setting DRQ.

5.1. ATA Command Set

Table 5-1 summarizes the ATA command set with the paragraphs that follow describing the individual commands and the task file for each.

Table 5-1. ATA Command Set

Class	COMMAND	Code	FR	sc	SN	CY	DH	LBA
1	Check Power Mode	E5h or 98h	-	-	-	-	D	-
1	Execute Drive Diagnostic	90h	-	-	-	-	D	-
1	Erase Sector(s) (Note 2)	C0h	-	Υ	Υ	Υ	Υ	Υ
2	Format Track	50h	-	Υ	-	Υ	Υ	Υ
1	Identify Drive	ECh	-	-	-	-	D	-
1	Idle	E3h or 97h	-	Υ	-	-	D	-
1	Idle Immediate	E1h or 95h	-	-	-	-	D	-
1	Initialize Drive Parameters	91h	-	Υ	-	-	Υ	-
1	Read Buffer	E4h	-	-	-	-	D	-
1	Read Multiple	C4h	-	Υ	Υ	Υ	Υ	Υ
1	Read Long Sector	22h or 23h	-	-	Υ	Υ	Υ	Υ
1	Read Sector(s)	20h or 21h	-	Υ	Υ	Υ	Υ	Υ
1	Read Verify Sector(s)	40h or 41h	-	Υ	Υ	Υ	Υ	Υ
1	Recalibrate	1Xh	-	-	-	-	D	-
1	Request Sense (Note 1)	03h	-	-	-	-	D	-
1	Seek	7Xh	-	-	Υ	Υ	Υ	Υ
1	Set Features	EFh	Υ	-	-	-	D	-
1	Set Multiple Mode	C6h	-	Υ	-	-	D	-
1	Set Sleep Mode	E6h or 99h	-	-	-	-	D	-
1	Stand By	E2h or 96h	-	-	-	-	D	-
1	Stand By Immediate	E0h or 94h	-	-	-	-	D	-

Class	COMMAND	Code	FR	sc	SN	CY	DH	LBA
1	Translate Sector (Note 1)	87h	-	Υ	Υ	Υ	Υ	Υ
1	Wear Level (Note 1)	F5h	-	-	-	-	Υ	ı
2	Write Buffer	E8h	-	-	-	-	D	-
2	Write Long Sector	32h or 33h	-	-	Υ	Υ	Υ	Υ
3	Write Multiple	C5h	-	Υ	Υ	Υ	Υ	Υ
3	Write Multiple w/o Erase (Note 2)	CDh	-	Υ	Υ	Υ	Υ	Υ
2	Write Sector(s)	30h or 31h	-	Y	Y	Y	Υ	Υ
2	Write Sector(s) w/o Erase (Note 2)	38h	-	Υ	Υ	Υ	Υ	Υ
2	Write Verify Sector(s)	3Ch	-	Υ	Υ	Υ	Υ	Υ

Note 1: These commands are not standard PC Card ATA commands but provide additional functionality.

Note 2: These commands are not standard PC Card ATA commands and these features are no longer supported with the introduction of 256 Mbit Flash Technology. If one of these commands is issued, the sectors will be erased but there will be no net gain in write performance when using the Write Without Erase command.

Definitions: FR = Features Register, SC = Sector Count Register, SN = Sector Number Register, CY = Cylinder Registers, DH = Card/Drive/Head Register, LBA = Logical Block Address Mode Supported (see command descriptions for use).

Y—The register contains a valid parameter for this command. For the Drive/Head Register Y means both the CompactFlash Card and head parameters are used; D—only the CompactFlash Card parameter is valid and not the head parameter.

5.1.1. Check Power Mode—98H, E5H

Table 5-2. Check Power Mode

Bit ->	7	6	5	4	3	2	1	0				
Command (7)		E5H or 98H										
C/D/H (6)		Х		Drive	X							
Cyl High (5)		X										
Cyl Low (4)				Х								
Sec Num (3)				Х								
Sec Cnt (2)		X										
Feature (1)				Х								

This command checks the power mode.

If the CompactFlash Memory Card is in, going to, or recovering from the sleep mode, the CompactFlash Card sets BSY, sets the Sector Count Register to 00h, clears BSY and generates an interrupt.

If the CompactFlash Memory Card is in Idle mode, the CompactFlash Card sets BSY, sets the Sector Count Register to FFh, clears BSY and generates an interrupt.

5.1.2. Execute Drive Diagnostic—90H

Table 5-3. Executive Drive Diagnostic

Bit ->	7	6	5	4	3	2	1	0				
Command (7)		90H										
C/D/H (6)		Х		Drive		>	(
Cyl High (5)		X										
Cyl Low (4)				Х								
Sec Num (3)				Х								
Sec Cnt (2)				Х								
Feature (1)				Х								

This command performs the internal diagnostic tests implemented by the CompactFlash Memory Card.

The Diagnostic codes shown in Table 5-4 are returned in the Error Register at the end of the command.

Table 5-4. Diagnostic Codes

Code	Error Type
01h	No Error Detected
02h	Formatter Device Error
03h	Sector Buffer Error
04h	ECC Circuitry Error
05h	Controlling Microprocessor Error
8Xh	Slave Failed (True IDE Mode)

5.1.3. Erase Sector(s)—C0H

Table 5-5. Erase Sectors

Bit ->	7	6	5	4	3	2	1	0			
Command (7)	СОН										
C/D/H (6)	1	LBA	1	Drive	Head (LBA 27-24)						
Cyl High (5)	Cylinder High (LBA 23-16)										
Cyl Low (4)				Cylinder Low	(LBA 15-8)						
Sec Num (3)				Sector Number	er (LBA 7-0))					
Sec Cnt (2)	Sector Count										
Feature (1)				Х							

This command is no longer recommended. There is essentially no net gain in the use of the Erase Sectors Command and/or the Write Without Erase Commands. This command is supported to guarantee backward compatibility.

5.1.4. Format Track—50H

Table 5-6. Format Track												
Bit ->	7	6	5	4	3	2	1	0				
Command (7)		50H										
C/D/H (6)	1	LBA	1	Drive	Head (LBA 27-24)							
Cyl High (5)		Cylinder High (LBA 23-16)										
Cyl Low (4)				Cylinder Lov	v (LBA 15-8)							
Sec Num (3)				X (LB	A 7-0)							
Sec Cnt (2)		Count (LBA mode only)										
Feature (1)				>	(

NOTE: The Format Track command in Table 5-6 is no longer recommended. The command is supported to guarantee backward compatibility.

This command writes the desired head and cylinder of the selected drive with an FFh pattern. To remain host backward compatible, the CompactFlash Memory Card expects a sector buffer of data from the host to follow the command with the same protocol as the Write Sector(s) command although the information in the buffer is not used by the CompactFlash Card. If LBA=1 then the number of sectors to format is taken from the Sec Cnt register (0=256).

5.1.5. Identify Drive—ECH

Table 5-7. Identify Drive												
Bit ->	7	6	5	4	3	2	1	0				
Command (7)		ECH										
C/D/H (6)	Χ	Х	Х	Drive			X					
Cyl High (5)		X										
Cyl Low (4)				;	X							
Sec Num (3)				;	X							
Sec Cnt (2)		Х										
Feature (1)					X							

The Identify Drive command enables the host to receive parameter information from the CompactFlash Memory Card. This command has the same protocol as the Read Sector(s) command. The parameter words in the buffer have the arrangement and meanings defined in Table 5-8. All reserved bits or words are zero. Table 5-8 is the definition for each field in the Identify Drive Information.

Table 5-8. Identify Drive Information

Word Address	Default Value	Total Bytes	Data Field Type Information				
0	848AH	2	General configuration bit-significant information				
1	XXXX	2	Default number of cylinders				
2	0000H	2	Reserved				

Word Address	Default Value	Total Bytes	Data Field Type Information
3	XXXX	2	Default number of heads
4	0000H	2	Number of unformatted bytes per track
5	0240H	2	Number of unformatted bytes per sector
6	XXXX	2	Default number of sectors per track
7-8	XXXX	4	Number of sectors per card (Word 7 = MSW, Word 8 = LSW)
9	0000H	2	Reserved
10-19	aaaa	20	Serial number in ASCII (Right Justified)
20	0002H	2	Buffer type (dual ported)
21	0002H	2	Buffer size in 512 byte increments
22	0004H	2	# of ECC bytes passed on Read/Write Long Commands
23-26	aaaa	8	Firmware revision in ASCII (Rev M.ms) set by code Big Endian Byte Order in Word
27-46	aaaa	40	Model number in ASCII (Left Justified) Big Endian Byte Order in Word
47	0001H	2	Maximum of 1 sector on Read/Write Multiple command
48	0000H	2	Double Word not supported
49	0200H	2	Capabilities: DMA NOT Supported (bit 8), LBA supported (bit 9)
50	0000H	2	Reserved
51	0200H	2	PIO data transfer cycle timing mode
52	0000H	2	DMA data transfer cycle timing mode Not Supported
53	0003	2	Field validity
54	0003H	2	Current numbers of cylinders
55	XXXX	2	Current numbers of heads
56	XXXX	2	Current sectors per track
57-58	XXXX	4	Current capacity in sectors (LBAs)(Word 57 = LSW, Word 58 = MSW)
59	010XH	2	Multiple sector setting is valid
60-61	XXXX	4	Total number of sectors addressable in LBA Mode
62-63	0000H	4	Reserved
64	0003H	2	Advanced PIO modes supported
65-66	0000H	4	Reserved
67	0078H	2	Minimum PIO transfer without flow control
68	0078H	2	Minimum PIO transfer with IORDY flow control
69-127	0000H	130	Reserved
128-159	0000H	64	Reserved vendor unique bytes
160-255	0000H	192	Reserved

5.1.5.1. Word 0: General Configuration

This field informs the host that this is a non-magnetic, hard sectored, removable storage device with a transfer rate greater than 10 mb/sec and is not MFM encoded. CompactFlash products report 848AH in compliance with the CFA specification.

5.1.5.2. Word 1: Default Number of Cylinders

This field contains the number of translated cylinders in the default translation mode. This value will be the same as the number of cylinders.

5.1.5.3. Word 3: Default Number of Heads

This field contains the number of translated heads in the default translation mode.

5.1.5.4. Word 4: Number of Unformatted Bytes per Track

This field contains the number of unformatted bytes per translated track in the default translation mode.

5.1.5.5. Word 5: Number of Unformatted Bytes per Sector

This field contains the number of unformatted bytes per sector in the default translation mode.

5.1.5.6. Word 6: Default Number of Sectors per Track

This field contains the number of sectors per track in the default translation mode.

5.1.5.7. Words 7-8: Number of Sectors per Card

This field contains the number of sectors per CompactFlash Memory Card. This double word value is also the first invalid address in LBA translation mode.

5.1.5.8. Words 10-19: Memory Card Serial Number

The contents of this field are right justified and padded with spaces (20h).

5.1.5.9. Word 20: Buffer Type

This field defines the buffer capability with the 0002h meaning a dual ported multi-sector buffer capable of simultaneous data transfers to or from the host and the CompactFlash Memory Card.

5.1.5.10. Word 21: Buffer Size

This field defines the buffer capacity of 2 sectors or 1 kilobyte of SRAM.

5.1.5.11. Word 22: ECC Count

This field defines the number of ECC bytes used on each sector in the Read and Write Long commands.

5.1.5.12. Words 23-26: Firmware Revision

This field contains the revision of the firmware for this product.

5.1.5.13. Words 27-46: Model Number

This field contains the model number for this product and is left justified and padded with spaces (20h).

5.1.5.14. Word 47: Read/Write Multiple Sector Count

This field contains the maximum number of sectors that can be read or written per interrupt using the Read Multiple or Write Multiple commands.

5.1.5.15. Word 48: Double Word Support

This field indicates this product will not support double word transfers.

5.1.5.16. Word 49: Capabilities

This field indicates this product will not support DMA Data transfers but does support LBA mode.

5.1.5.17. Word 51: PIO Data Transfer Cycle Timing Mode

This field defines the mode for PIO data transfer.

5.1.5.18. Word 52: Single Word DMA Data Transfer Cycle Timing Mode

This field states this product does not support any Single Word DMA data transfer mode.

5.1.5.19. Word 53: Translation Parameters Valid

Bit 0 of this field is set, indicating that words 54 to 58 are valid and reflect the current number of cylinders, heads and sectors. Bit 1 is also set, indicating values in words 64 through 70 are valid.

5.1.5.20. Words 54-56: Current Number of Cylinders, Heads, Sectors/Track

These fields contains the current number of user addressable Cylinders, Heads, and Sectors/Track in the current translation mode.

5.1.5.21. Words 57- 58: Current Capacity

This field contains the product of the current cylinders times heads times sectors.

5.1.5.22. Word 59: Multiple Sector Setting

This field contains a validity flag in the odd byte and the current number of sectors that can be transferred per interrupt for R/W Multiple in the even byte. The odd byte is always 01H, which indicates that the even byte is always valid.

The even byte value depends on the value set by the Set Multiple command. The even byte of this word by default contains a 00H, which indicates that R/W Multiple commands are not valid. The only other value returned by the CompactFlash Memory Card in the even byte is a 01H value, which indicates that 1 sector per interrupt, can be transferred in R/W Multiple mode.

5.1.5.23. Words 60-61: Total Sectors Addressable in LBA Mode

This field contains the number of sectors addressable for the CompactFlash Memory Card in LBA mode only.

5.1.5.24. Word 64: Advanced PIO Transfer Modes Supported

Bits 0 and 1 of this field are set to indicate support for PIO transfer modes 3 and 4, respectively.

5.1.5.25. Word 67: Minimum PIO Transfer Cycle Time Without Flow Control

This field indicates in nanoseconds, the minimum cycle time that, if used by the host, the CompactFlash Memory Card guarantees data integrity during the cycle without utilization of flow control.

5.1.5.26. Word 68: Minimum PIO Transfer Cycle Time With Flow Control

This field indicates in nanoseconds, the minimum cycle time the CompactFlash Memory Card supports while performing data transfers using flow control.

5.1.6. Idle—97H, E3H

Table 5-9. Idle													
Bit ->	7	6	5	4	3	2	1	0					
Command (7)		E3H or 97H											
C/D/H (6)		X Drive X											
Cyl High (5)		X											
Cyl Low (4)				Х									
Sec Num (3)				Х									
Sec Cnt (2)		Timer Count (5 msec increments)											
Feature (1)				Х	,								

This command causes the CompactFlash Memory Card to set BSY, enter the Idle (Read) mode, clear BSY and generate an interrupt. If the sector count is non-zero, it is interpreted as a timer count with each count being 5 milliseconds and the automatic power down mode is enabled. If the sector count is zero, the automatic power down mode is disabled. Note that this time base (5 msec) is different from the ATA specification.

5.1.7. Idle Immediate—95H, E1H

Table 5-10. Idle Immediate												
Bit ->	7	6	5	4	3	2	1	0				
Command (7)		E1H or 95H										
C/D/H (6)		Χ		Drive	X							
Cyl High (5)		X										
Cyl Low (4)				χ	(
Sec Num (3)				X	(
Sec Cnt (2)		Х										
Feature (1)				X	(

This command causes the CompactFlash Memory Card to set BSY, enter the Idle (Read) mode, clear BSY and generate an interrupt.

5.1.8. Initialize Drive Parameters—91H

Table 5-11. Initialize Drive Parameters Bit -> 7 0 5 1 91H Command (7) C/D/H (6) Χ 0 Χ Drive Max Head (no. of heads-1) Cyl High (5) Χ Cyl Low (4) Χ Sec Num (3) Χ Sec Cnt (2) Number of Sectors Χ Feature (1)

This command enables the host to set the number of sectors per track and the number of heads per cylinder. Only the Sector Count and the Card/Drive/Head registers are used by this command.

NOTE: SanDisk recommends NOT using this command in any system because DOS determines the offset to the Boot Record based on the number of heads and sectors per track. If a CompactFlash Memory Card is "Formatted" with one head and sector per track value, the same CompactFlash Card will not operate correctly with DOS configured with another heads and sectors per track value.

5.1.9. Read Buffer—E4H

Table 5-12. Read Buffer Bit -> 6 4 2 0 Command (7) E4H C/D/H (6) Χ Χ Drive Cyl High (5) Χ Χ Cyl Low (4) Χ Sec Num (3) Χ Sec Cnt (2) Feature (1) Χ

The Read Buffer command enables the host to read the current contents of the CompactFlash Memory Card's sector buffer. This command has the same protocol as the Read Sector(s) command.

5.1.10. Read Multiple—C4H

Table 5-13. Read Multiple												
Bit ->	7	6	5	4	3	2	1	0				
Command (7)		C4H										
C/D/H (6)	1	LBA	1	Drive	Head (LBA 27-24)							
Cyl High (5)		Cylinder High (LBA 23-16)										
Cyl Low (4)				Cylinder Lov	v (LBA 15-8)							
Sec Num (3)				Sector Numb	er (LBA 7-0)							
Sec Cnt (2)		Sector Count										
Feature (1))	(

NOTE: The current revision of the CompactFlash Memory Card only supports a block count of 1 as indicated in the Identify Drive Information command. This command is provided for compatibility with future products that may support a larger block count.

The Read Multiple command performs similarly to the Read Sectors command. Interrupts are not generated on every sector, but on the transfer of a block, which contains the number of sectors defined by a Set Multiple, command.

Command execution is identical to the Read Sectors operation except that the number of sectors defined by a Set Multiple command is transferred without intervening interrupts. DRQ qualification of the transfer is required only at the start of the data block, not on each sector.

The block count of sectors to be transferred without intervening interrupts is programmed by the Set Multiple Mode command, which must be executed prior to the Read Multiple command. When the Read Multiple command is issued, the Sector Count Register contains the number of sectors (not the number of blocks or the block count) requested. If the number of requested sectors is not evenly divisible by the block count, as many full blocks as possible are transferred, followed by a final, partial block transfer. The partial block transfer is for n sectors, where:

n = (sector count)—modulo (block count).

If the Read Multiple command is attempted before the Set Multiple Mode command has been executed or when Read Multiple commands are disabled, the Read Multiple operation is rejected with an Aborted Command error. Disk errors encountered during Read Multiple commands are posted at the beginning of the block or partial block transfer, but DRQ is still set and the data transfer will take place as it normally would, including transfer of corrupted data, if any.

Interrupts are generated when DRQ is set at the beginning of each block or partial block. The error reporting is the same as that on a Read Sector(s) Command. This command reads from 1 to 256 sectors as specified in the Sector Count register. A sector count of 0 requests 256 sectors. The transfer begins at the sector specified in the Sector Number Register.

At command completion, the Command Block Registers contain the cylinder, head and sector number of the last sector read.

If an error occurs, the read terminates at the sector where the error occurred. The Command Block Registers contain the cylinder, head and sector number of the sector where the error occurred. The flawed data is pending in the sector buffer.

Subsequent blocks or partial blocks are transferred only if the error was a correctable data error. All other errors cause the command to stop after transfer of the block that contained the error.

5.1.11. Read Long Sector—22H, 23H

-	Table 5-14. Read Long Sector												
7	6	5	4	3	2	1	0						
22H or 23H													
1	LBA	1	Drive	Head (LBA 27-24)									
Cylinder High (LBA 23-16)													
			Cylinder Lov	v (LBA 15-8)									
			Sector Numb	er (LBA 7-0))								
X													
			>	(
	1			22H o 1 LBA 1 Drive Cylinder High Cylinder Low Sector Numb	22H or 23H 1 LBA 1 Drive Cylinder High (LBA 23-16 Cylinder Low (LBA 15-8) Sector Number (LBA 7-0)	22H or 23H 1 LBA 1 Drive Head (LBA 23-16) Cylinder High (LBA 23-16) Cylinder Low (LBA 15-8) Sector Number (LBA 7-0) X	22H or 23H 1						

The Read Long command performs similarly to the Read Sector(s) command except that it returns 516 bytes of data instead of 512 bytes. During a Read Long command, the CompactFlash Memory Card does not check the ECC bytes to determine if there has been a data error. Only single sector read long operations are supported. The transfer consists of 512 bytes of data transferred in word mode followed by 4 bytes of random data transferred in byte mode. Random data is returned instead of ECC bytes because of the nature of the ECC system used. This command has the same protocol as the Read Sector(s) command.

5.1.12. Read Sector(s)—20H, 21H

Table 5-15. Read Sectors												
Bit ->	7	6	5	4	3	2	1	0				
Command (7)		20H or 21H										
C/D/H (6)	1	LBA	1	Drive	Head (LBA 27-24)							
Cyl High (5)		Cylinder High (LBA 23-16)										
Cyl Low (4)				Cylinder Low	/ (LBA 15-8)							
Sec Num (3)				Sector Numb	er (LBA 7-0))						
Sec Cnt (2)		Sector Count										
Feature (1)				Х	(

This command reads from 1 to 256 sectors as specified in the Sector Count register. A sector count of 0 requests 256 sectors. The transfer begins at the sector specified in the Sector Number Register. When this command is issued and after each sector of data (except the last one) has been read by the host, the CompactFlash Memory Card sets BSY, puts the sector of data in the buffer, sets DRQ, clears BSY, and generates an interrupt. The host then reads the 512 bytes of data from the buffer.

At command completion, the Command Block Registers contain the cylinder, head and sector number of the last sector read. If an error occurs, the read terminates at the sector where the error occurred. The Command Block Registers contain the cylinder, head, and sector number of the sector where the error occurred. The flawed data is pending in the sector buffer.

5.1.13. Read Verify Sector(s)-40H, 41H

Table 5-16. Read Verify Sectors Bit -> 4 2 7 6 5 0 40H or 41H Command (7) C/D/H (6) 1 LBA 1 Drive Head (LBA 27-24) Cyl High (5) Cylinder High (LBA 23-16) Cyl Low (4) Cylinder Low (LBA 15-8) Sec Num (3) Sector Number (LBA 7-0) Sec Cnt (2) Sector Count Χ Feature (1)

This command is identical to the Read Sectors command, except that DRQ is never set and no data is transferred to the host. When the command is accepted, the CompactFlash Memory Card sets BSY.

When the requested sectors have been verified, the CompactFlash Memory Card clears BSY and generates an interrupt. Upon command completion, the Command Block Registers contain the cylinder, head, and sector number of the last sector verified.

If an error occurs, the verify terminates at the sector where the error occurs. The Command Block Registers contain the cylinder, head and sector number of the sector where the error occurred. The Sector Count Register contains the number of sectors not yet verified.

5.1.14. Recalibrate—1XH

Table 5-17. Recalibrate												
Bit ->	7	6	5	4	3	2	1	0				
Command (7)		1XH										
C/D/H (6)	1	LBA	1	Drive		,	X					
Cyl High (5)		X										
Cyl Low (4))	X							
Sec Num (3))	X							
Sec Cnt (2)		X										
Feature (1))	X							

This command is effectively a NOP command to the CompactFlash Memory Card and is provided for compatibility purposes. After this command is executed the Cyl High and Cyl Low as well as the Head number will be 0 and Sec Num will be 1 if LBA=0 and 0 if LBA=1 (i.e., the first block in LBA is 0 while CHS mode the sector number starts at 1).

5.1.15. Request Sense—03H

Table 5-18. Request Sense

				- · · · · · · · · · · · · · · · · · · ·							
Bit ->	7	6	5	4	3	2	1	0			
Command (7)		03H									
C/D/H (6)	1	Х	1	Drive		>	(
Cyl High (5)		X									
Cyl Low (4)				Х							
Sec Num (3)				Х							
Sec Cnt (2)		X									
Feature (1)				Х							

This command requests an extended error code after a command ends with an error. Table 5-19 defines the valid extended error codes for the CompactFlash Memory Card Series product. The extended error code is returned to the host in the Error Register. This command must be the next command issued to the CompactFlash Card following the command that returned an error.

Table 5-19. Extended Error Codes

Extended Error Code	Description
00h	No Error Detected
01h	Self Test OK (No Error)
09h	Miscellaneous Error
20h	Invalid Command
21h	Invalid Address (Requested Head or Sector Invalid)
2Fh	Address Overflow (Address Too Large)
35h, 36h	Supply or generated Voltage Out of Tolerance
11h	Uncorrectable ECC Error
18h	Corrected ECC Error
05h, 30-34h, 37h, 3Eh	Self Test or Diagnostic Failed
10h, 14h	ID Not Found
3Ah	Spare Sectors Exhausted
1Fh	Data Transfer Error/Aborted Command
0Ch, 38H, 3Bh, 3Ch, 3Fh	Corrupted Media Format
03h	Write/Erase Failed

5.1.16. Seek-7XH

Table 5-20. Seek

Bit ->	7	6	5	4	3	2	1	0			
Command (7)		7XH									
C/D/H (6)	1	LBA	1	Drive Head (LBA 27-24)							
Cyl High (5)		Cylinder High (LBA 23-16)									
Cyl Low (4)				Cylinder Low	(LBA 15-8)						
Sec Num (3)				X (LBA	7-0)						
Sec Cnt (2)		Х									
Feature (1)	•			Х							

This command is effectively a NOP command to the CompactFlash Memory Card although it does perform a range check of cylinder and head or LBA address and returns an error if the address is out of range.

5.1.17. Set Features—EFH

Table 5-21. Seat Features

Bit ->	7	6	5	4	3	2	1	0		
Command (7)		EFH								
C/D/H (6)		Х		Drive			X			
Cyl High (5)		X								
Cyl Low (4)				Х						
Sec Num (3)				Х						
Sec Cnt (2)		Config								
Feature (1)				Feat	ure					

This command is used by the host to establish or select certain features. Table 5-22 defines all features that are supported. Please note that the 9AH feature is unique to the CompactFlash Memory Card and are not part of the ATA Specification.

Table 5-22. Features Supported

Feature	Operation
01H	Enable 8-bit data transfer.
03H	Set Transfer Mode based on value and Sector Count register.
55H	Disable Read Look Ahead.
66H	Disable Power on Reset (POR) establishment of defaults at Soft Reset.
69H	Accepted for backward compatibility with the SDP Series but has no impact on the CF Memory Card.
81H	Disable 8-bit data transfer.
96H	Accepted for backward compatibility with the SDP Series but has no impact on the CF Memory Card.
9AH	Accepted for backward compatibility with the SDP Series but has no impact on the CF Memory Card.
BBH	4 bytes of data apply on Read/Write Long commands.
CCH	Enable Power on Reset (POR) establishment of defaults at Soft Reset.

Features 01H and 81H are used to enable and clear 8 bit data transfer mode. If the 01H feature command is issued, all data transfers will occur on the low order D7-D0 data bus and the IOIS16 signal will not be asserted for data register accesses.

A host can choose the transfer mechanism by Set Transfer Mode and specifying a value in the Sector Count register. The upper 5 bits define the type of transfer and the low order 3 bits encode the mode value.

PIO Default Transfer Mode	00000 00d
PIO Flow Control Transfer Mode x	00001 nnn
Multiword DMA Mode x	00100 nnn
Reserved	01000 nnn
Reserved	10000 nnn

Where "nnn" is a valid mode number in binary, "x" is the mode number in decimal for the associated transfer type, and "d" is ignored.

Features 55H and BBH are the default features for the CompactFlash Memory Card; thus, the host does not have to issue this command with these features unless it is necessary for compatibility reasons.

The 9AH Feature is accepted for backward compatibility with the SDP Series but has no impact on the CompactFlash Memory Card. SanDisk does not recommend the use of this command in new designs.

Features 66H and CCH can be used to enable and disable whether the Power On Reset (POR) Defaults will be set when a soft reset occurs. The default setting is to revert to the POR defaults when a soft reset occurs. POR defaults the number of heads and sectors along with 16 bit data transfers and the read/write multiple block count.

5.1.18. Set Multiple Mode—C6H

Sec Num (3) Sec Cnt (2)

Feature (1)

7 5 4 Bit -> 6 2 1 Command (7) C6H C/D/H (6) Χ Χ Drive Cyl High (5) Χ Χ Cyl Low (4)

Χ

Sector Count

Χ

Table 5-23. Seat Multiple Mode

This command enables the CompactFlash Card to perform Read and Write Multiple operations and establishes the block count for these commands. The Sector Count Register is loaded with the number of sectors per block. The current version of the CompactFlash Card supports only a block size of 1 sector per block. Future versions may support larger block sizes. Upon receipt of the command, the CompactFlash Card sets BSY to 1 and checks the Sector Count Register.

0

If the Sector Count Register contains a valid value and the block count is supported, the value is loaded for all subsequent Read Multiple and Write Multiple commands and execution of those commands is enabled. If a block count is not supported, an Aborted Command error is posted, and Read Multiple and Write Multiple commands are disabled. If the Sector Count Register contains 0 when the command is issued, Read and Write Multiple commands are disabled. At power on, or after a hardware or (unless disabled by a Set Feature command) software reset, the default mode is Read and Write Multiple disabled.

5.1.19. Set Sleep Mode- 99H, E6H

Table 5-24. Set Sleep Mode												
Bit ->	7	6	5	4	3	2	1	0				
Command (7)		E6H or 99H										
C/D/H (6)		Х		Drive		,	X					
Cyl High (5)		X										
Cyl Low (4)				Х								
Sec Num (3)				Х								
Sec Cnt (2)				Х								
Feature (1)		•		Х								

This command causes the CompactFlash Memory Card to set BSY, enter the Sleep mode, clear BSY and generate an interrupt. Recovery from sleep mode is accomplished by simply issuing another command (a reset is permitted but not required). Sleep mode is also entered when internal timers expire so the host does not need to issue this command except when it wishes to enter Sleep mode immediately. The default value for the read to sleep timer is 5 milliseconds. Note that this time base (5 msec) is different from the ATA Specification.

5.1.20. Standby—96H, E2H

Table 5-25. Standby												
Bit ->	7	6	5	4	3	2	1	0				
Command (7)		E2H or 96H										
C/D/H (6)		Χ		Drive			X					
Cyl High (5)		X										
Cyl Low (4)				2	X							
Sec Num (3)				2	X							
Sec Cnt (2)		X										
Feature (1)				2	X							

This command causes the CompactFlash Memory Card to set BSY, enter the Sleep mode (which corresponds to the ATA "Standby" Mode), clear BSY and return the interrupt immediately. Recovery from sleep mode is accomplished by simply issuing another command (a reset is not required).

5.1.21. Standby Immediate—94H, E0H

Table 5-26. Standby Immediate

Bit ->	7	6	5	4	3	2	1	0			
Command (7)		E0H or 94H									
C/D/H (6)		Χ		Drive		2	X				
Cyl High (5)		X									
Cyl Low (4)				Х							
Sec Num (3)				Х							
Sec Cnt (2)		X									
Feature (1)	·	·	·	Х		·	·				

This command causes the CompactFlash Memory Card to set BSY, enter the Sleep mode (which corresponds to the ATA "Standby" Mode), clear BSY and return the interrupt immediately. Recovery from sleep mode is accomplished by simply issuing another command (a reset is not required).

5.1.22. Translate Sector—87H

Table 5-27. Translate Sector

Bit ->	7	6	5	4	3	2	1	0		
Command (7)		87H								
C/D/H (6)	1	LBA	1	Drive	Head (LBA 27-24)					
Cyl High (5)		Cylinder High (LBA 23-16)								
Cyl Low (4)		Cylinder Low (LBA 15-8)								
Sec Num (3)		Sector Number (LBA 7-0)								
Sec Cnt (2)		X								
Feature (1)				>	(

When this command is issued, the controller responds with a 512-byte buffer of information on the desired cylinder, head and sector with the actual Logical Address. Table 5-28 represents the information in the buffer. Please note that this command is unique to the SanDisk CompactFlash Memory Card.

Table 5-28. Translate Sector Information

Address	Information
00	Head
01-02	Cylinder
03	Sector
04-07	LBA
08	Chip
09-0A	Block
0B	Page
0C-1FF	Reserved

5.1.23. Wear Level—F5H

Table 5-29. Wear Level Bit -> 7 6 5 4 3 2 0 Command (7) F5H C/D/H (6) Χ Χ Χ Drive Flag Cyl High (5) Χ Cyl Low (4) Χ Sec Num (3) Χ Sec Cnt (2) **Completion Status** Feature (1) Χ

This command is effectively a NOP command and only implemented for backward compatibility with earlier SanDisk SDP series products. The Sector Count Register will always be returned with an 00H indicating Wear Level is not needed.

5.1.24. Write Buffer—E8H

Table 5-30. Write Buffer									
Bit ->	7	6	5	4	3	2	1	0	
Command (7)				E	8H				
C/D/H (6)		Χ		Drive			X		
Cyl High (5)				2	X				
Cyl Low (4)					X				
Sec Num (3)				;	X				
Sec Cnt (2)				2	X				
Feature (1)					X				

The Write Buffer command enables the host to overwrite contents of the CompactFlash Memory Card's sector buffer with any data pattern desired. This command has the same protocol as the Write Sector(s) command and transfers 512 bytes.

5.1.25. Write Long Sector—32H, 33H

Table 5-31. Write Long Sector											
Bit ->	7	6	5	4	3	2	1	0			
Command (7)		32H or 33H									
C/D/H (6)	1	1 LBA 1 Drive Head (LBA 27-24)									
Cyl High (5)		Cylinder High (LBA 23-16)									
Cyl Low (4)		Cylinder Low (LBA 15-8)									
Sec Num (3)		Sector Number (LBA 7-0)									
Sec Cnt (2)		Х									
Feature (1))	(

This command is provided for compatibility purposes and is similar to the Write Sector(s) command except that it writes 516 bytes instead of 512 bytes. Only single sector Write Long operations are supported. The transfer consists of 512 bytes of data transferred in word mode followed by 4 bytes of ECC transferred in byte mode. Because of the unique nature of the solid-state CompactFlash Memory Card, the four bytes of ECC transferred by the host cannot be used by the CompactFlash Card. The CompactFlash Card discards these four bytes and writes the sector with valid ECC fields. This command has the same protocol as the Write Sector(s) command.

5.1.26. Write Multiple Command—C5H

Table 5-32. Write Multiple Command										
Bit ->	7	6	5	4	3	2	1	0		
Command (7)		C5H								
C/D/H (6)	Χ	LBA	Х	Drive	Head					
Cyl High (5)		Cylinder High								
Cyl Low (4)		Cylinder Low								
Sec Num (3)		Sector Number								
Sec Cnt (2)		Sector Count								
Feature (1)		Х								

NOTE: The current revision of the CompactFlash Memory Card only supports a block count of 1 as indicated in the Identify Drive Command information. This command is provided for compatibility with future products that may support a larger block count.

This command is similar to the Write Sectors command. The CompactFlash Memory Card sets BSY within 400 nsec of accepting the command. Interrupts are not presented on each sector but on the transfer of a block that contains the number of sectors defined by Set Multiple. Command execution is identical to the Write Sectors operation except that the number of sectors defined by the Set Multiple command is transferred without intervening interrupts.

DRQ qualification of the transfer is required only at the start of the data block, not on each sector. The block count of sectors to be transferred without intervening interrupts is programmed by the Set Multiple Mode command, which must be executed prior to the Write Multiple command.

When the Write Multiple command is issued, the Sector Count Register contains the number of sectors (not the number of blocks or the block count) requested. If the number of requested sectors is not evenly divisible by the sector/block, as many full blocks as possible are transferred, followed by a final, partial block transfer. The partial block transfer is for n sectors, where:

n = remainder (sector count/block count).

If the Write Multiple command is attempted before the Set Multiple Mode command has been executed or when Write Multiple commands are disabled, the Write Multiple operation will be rejected with an aborted command error.

Errors encountered during Write Multiple commands are posted after the attempted writes of the block or partial block transferred. The Write command ends with the sector in error, even if it is in the middle of a block. Subsequent blocks are not transferred in the event of an error. Interrupts are generated when DRQ is set at the beginning of each block or partial block.

The Command Block Registers contain the cylinder, head and sector number of the sector where the error occurred and the Sector Count Register contains the residual number of sectors that need to be transferred for successful completion of the command e.g., each block has 4 sectors, a request for 8 sectors is issued and an error occurs on the third sector. The Sector Count Register contains 6 and the address is that of the third sector.

5.1.27. Write Multiple without Erase—CDH

Table 5-33. Write Multiple without Erase										
Bit ->	7	6	5	4	3	2	1	0		
Command (7)		CDH								
C/D/H (6)	Χ	LBA	Х	Drive		Не	ead			
Cyl High (5)		Cylinder High								
Cyl Low (4)		Cylinder Low								
Sec Num (3)		Sector Number								
Sec Cnt (2)		Sector Count								
Feature (1)		Х								

SanDisk does not recommend the use of this command in new designs but it is supported as a normal Write Sectors command for backward compatibility reasons.

5.1.28. Write Sector(s)—30H, 31H

		Ta	able 5-34.	. Write Sec	etors					
Bit ->	7	6	5	4	3	2	1	0		
Command (7)		30H or 31H								
C/D/H (6)	1	LBA	1	Drive		Head (LI	BA 27-24)			
Cyl High (5)		Cylinder High (LBA 23-16)								
Cyl Low (4)		Cylinder Low (LBA 15-8)								
Sec Num (3)		Sector Number (LBA 7-0)								
Sec Cnt (2)		Sector Count								
Feature (1))	(

This command writes from 1 to 256 sectors as specified in the Sector Count Register. A sector count of zero requests 256 sectors. The transfer begins at the sector specified in the Sector Number Register. When this command is accepted, the CompactFlash Memory Card sets BSY, then sets DRQ and clears BSY, then waits for the host to fill the sector buffer with the data to be written. No interrupt is generated to start the first buffer fill operation. No data should be transferred by the host until BSY has been cleared by the host.

For multiple sectors, after the first sector of data is in the buffer, BSY will be set and DRQ will be cleared. After the next buffer is ready for data, BSY is cleared, DRQ is set and an interrupt is generated. When the final sector of data is transferred, BSY is set and DRQ is cleared. It will remain in this state until the command is completed at which time BSY is cleared and an interrupt is generated.

If an error occurs during a write of more than one sector, writing terminates at the sector where the error occurs. The Command Block Registers contain the cylinder, head and sector number of the sector where the error occurred. The host may then read the command block to determine what error has occurred, and on which sector.

5.1.29. Write Sector(s) without Erase—38H

Table 5-35. Write Sectors without Erase Bit -> 7 5 2 0 Command (7) 38H C/D/H (6) 1 LBA 1 Drive Head (LBA 27-24) Cyl High (5) Cylinder High (LBA 23-16) Cyl Low (4) Cylinder Low (LBA 15-8) Sec Num (3) Sector Number (LBA 7-0) Sec Cnt (2) Sector Count Χ Feature (1)

SanDisk does not recommend the use of this command in new designs but it is supported as a normal Write Sectors command for backward compatibility reasons.

5.1.30. Write Verify Sector(s)-3CH

	Table 5-36. Writer Verify Sectors														
Bit ->	7	6	5	4	3	2	1	0							
Command (7)				3C	Н										
C/D/H (6)	1 LBA 1 Drive Head (LBA 27-24)														
Cyl High (5)	Cylinder High (LBA 23-16)														
Cyl Low (4)				Cylinder Low	(LBA 15-8)										
Sec Num (3)				Sector Numb	er (LBA 7-0)										
Sec Cnt (2)	Sector Count														
Feature (1)				Х											

This command writes from 1 to 256 sectors as specified in the Sector Count Register. A sector count of zero requests 256 sectors. The transfer begins at the sector specified in the Sector Number Register. When this command is accepted, the CompactFlash Memory Card sets BSY, then sets DRQ and clears BSY, then waits for the host to fill the sector buffer with the data to be written. No interrupt is generated to start the first buffer fill operation. No data should be transferred by the host until BSY has been cleared by the host.

For multiple sectors, after the first sector of data is in the buffer, BSY will be set and DRQ will be cleared. After the next buffer is ready for data, BSY is cleared, DRQ is set and an interrupt is generated. When the final sector of data is transferred, BSY is set and DRQ is cleared. It will remain in this state until the command is completed at which time BSY is cleared and an interrupt is generated.

If an error occurs during a write of more than one sector, writing terminates at the sector where the error occurs. The Command Block Registers contain the cylinder, head and sector number of the sector where the error occurred. The host may then read the command block to determine what error has occurred, and on which sector.

5.2. Error Posting

Table 5-37 summarizes the valid status and error value for all the ATA Command set.

Table 5-37. Error and Status Register

Command		E	rror Regist	ter			Sta	atus Regis	ter	
	BBK	UNC	IDNF	ABRT	AMNF	DRDY	DWF	DSC	CORR	ERR
Check Power Mode				V		٧	٧	٧		V
Execute Drive Diagnostic*						V		V		V
Erase Sector(s)	V		V	V	V	V	V	V		V
Format Track			V	V	V	V	V	V		V
Identify Drive				V		V	V	V		V
Idle				V		V	V	V		V
Idle Immediate				V		V	V	V		V
Initialize Drive Parameters						V		V		V
Read Buffer				V		V	V	V		V

Command		Е	rror Regis	ter			St	atus Regis	ter	
	BBK	UNC	IDNF	ABRT	AMNF	DRDY	DWF	DSC	CORR	ERR
Read Multiple	V	V	V	V	٧	V	٧	V	V	V
Read Long Sector	V		V	V	V	V	٧	V		V
Read Sector(s)	V	V	V	V	V	V	٧	V	V	V
Read Verify Sectors	V	V	V	V	V	٧	V	V	V	V
Recalibrate				V		٧	V	V		V
Request Sense				V		٧		V		V
Seek			V	V		V	٧	V		V
Set Features				V		٧	٧	V		V
Set Multiple Mode				V		V	V	V		V
Set Sleep Mode				V		V	٧	V		V
Stand By				٧		V	٧	V		V
Stand By Immediate				V		٧	٧	V		V
Translate Sector	V		V	V	V	V	٧	V		V
Wear Level	V	V	V	V	V	V	٧	V		V
Write Buffer				V		V	٧	V		V
Write Long Sector	V		V	V	V	V	٧	V		V
Write Multiple	V		V	V	V	V	٧	V		V
Write Multiple w/o Erase	V		V	V	٧	٧	٧	V		V
Write Sector(s)	V		V	V	٧	٧	٧	V		V
Write Sector(s) w/o Erase	V		V	V	V	V	V	V		V
Write Verify Sector(s)	V		V	V	V	V	V	V		V
Invalid Command Code				V		V	٧	V		V

V =valid on this command

^{*} See Table 5-2.

6. CIS Description

This section describes the Card Information Structure (CIS) for the CompactFlash Memory Card.

Table 6-1. Card Information Structure

Attribute Offset	Data	7		6	5	4	3	2	1	0	Description of Contents	CIS Function		
000h	01h		1	ı	CIS	STPL	DE\	/ICE	1		Device Info Tuple	Tuple Code		
002h	03h										Link is 3 bytes	Link to next Tuple		
004h	D9			v ID ⁻ Oh = 1		е	W 1	1	Spee h =25		I/O Device, No WPS, speed=250ns if no wait	Device ID, WPS, Speed		
006h	01h		#	addre = ^	ess 1 ur		1		e Coo K uni		(One) 2 Kilobytes of address space	Device Size		
008h	FFh				Lis	st En	d Ma	rker			End of device info field	End Marker		
00Ah	1Ch			CI	ISTI	PL_D	EVIC	E_O	С		Other Conditions Info Tuple	Tuple Code		
00Ch	05h										Link is 5 bytes	Link to next tuple		
00Eh	03h		Reserved 3 V								Conditions: 3V operation is allowed, and WAIT is used	3 Volts Operation, Wait Function		
010h	D9h	Dev ID Type W Speed 1									I/O Device, No WPS, speed = 250 ns if no wait	Device ID, WPS, Speed		
012h	01h	#8		dress = 1 u		it-1	Siz		ode = nits	2K	(One) 2Kilobytes of address space	Device Size		
014h	FFh				Lis	st En	d Ma	rker			End of device info field	End Marker		
016h	00h					Not	Used				Note used	Not Used		
018h	18h			(CIS	TPL_	JEDE	EC_C	;		JEDEC ID Common Mem	Tuple Code		
01Ah	02h										Link is 2 bytes	Link Length		
01Ch	DFh	F	PCI	MCIA	JE	DEC	Man	ufact	urer's	ID	First Byte of JEDEC ID for SanDisk PC Card-ATA 12V	Byte 1, JEDEC ID of Device 1 (0-2K)		
01Eh	01h				Ρ	ССа	Cod Ird-A Requ	TA			Second Byte of JEDEC ID	Byte 2, JEDEC ID		
020h	20h				CIS	TPL	MAN	NFID			Manufacturer's ID Tuple	Tuple Code		
022h	04h										Link is 4 bytes	Link Length		
024h	45h	Low Byte of PCMCIA Manufacturer's Code									SanDisk JEDEC Manufacturer's ID	Low Byte of PCMCIA Mfg ID		
026h	00h	Hi	igh	Byte	of		CIA Node	Manu	factur	er's	Code of 0 because other byte is JEDEC 1 byte Manufacturer's ID	High Byte of PCMCIA Mfg ID		
028h	01h			Low	Ву	te of	Prod	uct C	ode		SanDisk Code for SDP Series	Low Byte Product Code		
02Ah	04h			High	ı Ву	te of	Prod	uct C	ode		SanDisk Code for PC Card ATA High Byte Product Cod			

Attribute Offset	Data	7	6	5	4	3	2	1	0	Description of Contents	CIS Function
02Ch	15h			CIS	TPI	_VE	R_1	ı	ı	Level 1 version/product info	Tuple Code
02Eh	17h									Link to next tuple is 23 bytes	Link Length
030h	04h			TPP	LV1	_MA	JOR			PCMCIA 2.0/JEIDA 4.1	Major Version
032h	01h			TPP	LV1	1_MI	NOR			PCMCIA 2.0/JEIDA 4.1	Minor Version
034h	53h		Α	SCII Ma	anu	factu	rer St	ring		'S'	String 1
036h	75h									'a' ¹	
038h	6Eh									'n'	
03Ah	44h									'D'	
03Ch	69h									'l'	
03Eh	73h									's'	
040h	6Bh									'k'	
042h	00h		Eı	nd of Ma	anu	factu	rer S	tring		Null terminator	
044h	53h		AS	SCII Pro	oduc	ct Na	me S	tring		'S'	Info String 2
046h	44h									'D'	
048h	50h									'P'	
04Ah	00h		En	d of Pro	odu	ct Na	me S	String		Null terminator	
04Ch	35h									'5'	Info String 3
04Eh	2Fh									'/'	
050h	33h									'3'	
052h	20h									11	
054h	30h	S	SanDis	sk Card	CIS	S Rev	vision	Num	ber	'0'	
056h	2Eh										
058h	36h									'6'	
05Ah	00h		En	d of CIS	S Re	evisio	n Nu	mber		Null terminator	
05Ch	FFh			End	of L	ist M	arker			FFh List terminator	No Info String 4
05Eh	80h		CIS	STPL_V	/EN	ID_S	PECI	F_80		SanDisk Parameters Tuple	Tuple Code
060h	03h		(F	ield Byt	es 3	3-4 ta	iken a	as 0)		Link length is 3 byte	Link to next tuple and length of info in this tuple

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 $^{^{\}rm 1}$ Legacy CompactFlash products may report "SunDisk" as the ASCII manufacture string.

Attribute Offset	Data	7	6	5	4	3	2	1	0	Description of Contents	CIS Function
062h	14h	W 0	0	0	PP 1	P D N A 0	R I A 1	R I R	SP 0	No Wear Level & NO Vpp W:No Wear Level 12:Vpp Not used on Write NI:-INPACK connected PP:Programmable Power PDNA:Pwr Down Not AbortCmd RIA:RBsy, ATBsy connected RIR:RBsy Inhibited at Reset SP:No Security Present This definition applies only to cards with Manufacturer's ID tuple 1st 3 bytes 45 00 01.	SanDisk Fields, 1 to 4 bytes limited by link length.
064h	08h	R 0	P A R R							R8:8 bit ROM present TAR:Temp Bsy on AT Reset TPR:Temp Bsy on PCMCIA Reset E:Erase Ahead Available R:Reserved, 0 for now This definition applies only to card with Manufacturer's ID tuple 1st 3 bytes 45 00 01.	SanDisk Fields, 1 to 4 bytes limited by link length.
066h	00h								•		For Specific platform use Only
068h	21h			CI	STPL	_FUN	NCID			Function ID Tuple	Tuple Code
06Ah	02h									Link length is 2 bytes	Link to next tuple
06Ch	04h			Fun	ction	Туре	Code	е		Disk Function	Function Code
06Eh	01h	R 0	R 0	R 0	R 0	R 0	R 0	R 0	P 1	Attempt installation at Post P:Install at POST R:Reserved(0)	
070h	22h			Cl	STPL	FUI	NCE		I	Function Extension Tuple	Tuple Code
072h	02h									Link length is 2 bytes	Link to next tuple
074h	01h	D	isk F	unctio	on Ex	tensio	on Tu	ple T	ype	Extension tuple describes the Interface Protocol	Extension Tuple Type for Disk
076h	01h			Inte	rface	Туре	Cod	е		PC Card-ATA Interface	Extension Info
078h	22h			CIS	STPL	_FUN	ICE			Function Extension tuple	Tuple Code
07Ah	03h									This tuple has 3 info bytes	Link Length
07Ch	02h	Di	sk Fu	ınctio	n Ext	ensio	n Tup	ole Ty	ре	Basic PCMCIA-ATA Extension tuple	Extension Tuple Type for Disk
07Eh	0Ch				F	₹				R	R
					()				0	0

Attribute Offset	Data	7	6	5	4	3	2	1	0	Description of Contents	CIS Function
07Eh	0Ch	R 0	R 0	R 0	R 0	U 1	S 1)	No Vpp, Silicon Drive with Unique Manufacturer/Serial Number combined string V=0:No Vpp Required V=1:Vpp on Modify Media V=2:Vpp on any operation V=3:Vpp continuous S:Silicon, else Rotating U:ID Drive Mfg/SN Unique	Basic ATA Option Parameters
080h	0Fh	R 0	0	E 0	N 0	P3	P2 1	P1	P0 1	All power down modes and power commands are not needed to minimize power. P0:Sleep Mode Supported P1:Standby Mode Supported P2:Idle Mode Supported P3:Drive Auto Power Control N:Some Config Excludes 3X7 E:Index Bit is Emulated I:Twin -IOis16 Data Reg Only	Extended ATA Option Parameters
082h	1Ah			CI	ISTPL	_CO	NF	•		Configuration Tuple	Tuple Code
084h	05h									Link Length is 5 bytes	Link to next tuple
086h	01h		RFS 00		RM 0	MS O		01		Size of Reserved Field is 0 bytes, Size of Register Mask is 1 Byte, Size of Config Base Address is 2 bytes RFS:Bytes in Reserved Field RMS:Bytes in Reg Mask-1 RAS:Bytes in Base Addr-1	Size of fields byte (TPCC_SZ)
088h	07h			7	ГРСС	_LAS	T			Entry with Config Index of 07h is final entry in table	Last entry of configuration table
08Ah	00h			TPO	CC_R	ADR	(lsb)			Configuration Registers are	Location of
08Ch	02h			TPC	C_R	ADR ((msb)			located at 200h in Reg Space.	Config Registers
08Eh	0Fh	R 0	R 0	R 0	R 0	S 1	P 1	P C I		First 4 Configuration Registers are present I:Configuration Index C:Configuration and Status P:Pin Replacement S:Socket and Copy R:Reserved for future use	TPCC_RMSK
090h	1Bh				CISTI	PL_C	E			Configuration Entry Tuple	Tuple Code
092h	0Bh									Link to next tuple is 11 bytes. Also limits size of this tuple to 13 bytes.	Link to next tuple

Attribute Offset	Data	7	6	5	4	3	2	1	0	Description of Contents	CIS Function
094h	C0h	1	D 1		Cor	nfigura	ation 0	Index	(Memory Mapped I/O Configuration Configuration Index for this entry is 0. Interface Byte follows this byte. Default Configuration, so is not dependent on previous Default Configuration. D:Default Configuration I:Interface Byte Follows	TPCE_INDX
096h	C0h	W 1	R 1	P 0	B 0	Ir		ce Ty 0	rpe	Memory Only Interface(0), Bvd's and wProt not used, Ready/-Busy and Wait for memory cycles active. B:Battery Volt Detects Used P:Write Protect Used R:Ready/-Busy Used W:Wait Used for Memory Cycles	TPCE_IF
098h	A1h	M 1		is 1	IR 0	1O 0	T 0		P 1	Vcc only Power; No Timing, I/O, or IRQ; 2 Byte Mem Space Length; Misc Entry Present P:Power info type T:Timing info present IO:I/O port info present IR:Interrupt info present MS:Mem space info type M:Misc info byte(s) present	TPCE_FS
09Ah	27h	R 0	DI 0	PI 1	AI 0	SI 0	HV 1	LV 1	NV 1	Nominal Voltage Follows NV:Nominal Voltage LV:Mimimum Voltage HB:Maximum Voltage SI:Static Current Al:Average Current PI:Peak Current DI:Power Down Current	Power Parameters for Vcc
09Ch	55h	X 0			ntissa = 5.0	l		xpon 5h = 1		Vcc Nominal is 5 Volts	Vcc Nominal Value
09Eh	4Dh	X 0			ntissa = 4.5			xpon 5h = ´		Vcc Nominal is 4.5 Volts	Vcc Minimum Value
0A0h	5Dh	X 0			ntissa = 5.5			xpon 5h = ´		Vcc Nominal is 5.5 Volts	Vcc Maximum Value
0A2h	75h	X 0			ntissa = 8.0			Exponent 5h = 10		Max Average Current over 10 msec is 80 mA	Max Average Current
0A4h	08h		Leng	jth in	256 b	ytes	page	s (Isb)	Length of Mem Space is 2 KB	TPCE_MS Length LSB
0A6h	00h		Leng	th in 2	256 by	ytes p	ages	(mst	D)	Start at 0 on card	TPCE_MS Length MSB

Attribute Offset	Data	7	6	5	4	3	2	1	0	Description of Contents	CIS Function			
0A8h	21h	X 0	R 0	P 1	RO 0	A 0		T 1		Power-Down, and Twin Card. T:Twin Cards Allowed A:Audio Supported RO:Read Only Mode P:Power Down Supported R:Reserved X:More Misc Fields Bytes	TPCE_MI			
0AAh	1Bh				CIST	PL_C	E			Configuration Entry Tuple	Tuple Code			
0ACh	06h									Link to next tuple is 6 bytes. Also limits size of this tuple to 8 bytes.	Link to next tuple			
0AEh	00h	1	D		Cor	nfigura		Index	(Memory mapped I/O 3.3V configuration.	TPCE_INDX			
	241	0	0				0	l .						
0B0h	01h	М	I	1S	IR	10	T	ŀ	0	P:Power info type	TPCE_FS			
		0	(0	0	0	0		1					
0B2h	21h	R 0	DI 0	PI 1	AI 0	SI 0	H 0	LV 0	NV 1	PI:Peak Current NV:Nominal Operation Supply Voltage	TPCE_PD			
0B4h	B5h	X 1			ntissa = 3.0			xpon 5h =		Nominal Operation Supply Voltage = 3.0V	Nominal Operation Supply Voltage			
0B6h	1Eh	X 0				1Eh				+.30	Nominal Operation Supply Voltage Extension Byte			
0B8h	4Dh	X 0		Mantissa Exponent 9h = 4.5 5h = 10						Max Average Current over 10 msec is 45mA	Max Average Current			
0BAh	1Bh				CIST	PL_C	E			Configuration Entry Tuple	Tuple Code			
0BCh	0Dh									Link to next tuple is 13 bytes. Also limits size of this tuple to 15 bytes.	Link to next tuple			
0BEh	C1h	1	D 1		Cor	nfigura	ation	Index	(I/O Mapped Contiguous 16 registers configuration Configuration Index for this entry is 1. Interface Byte follows this byte. Default Configuration, so is not dependent on previous Default Configuration. D:Default Configuration I:Interface Byte Follows	TPCE_INDX			
0C0h	41h	W 0	R 1	P 0	B 0	Ir	nterface Type						I/O Interface(1), Bvd's and wProt not used; Ready/-Busy active but Wait not used for memory cycles. B:Battery Volt Detects Used P:Write Protect Used R:Ready/-Busy Used W:Wait Used for Memory Cycles	TPCE_IF

Attribute Offset	Data	7	6	5	4	3	2	1	0	Description of Contents	CIS Function
0C2h	99h	M 1	MS 0	IR 1	10 1			T 0		P 1	Vcc Only Power Descriptors; No Timing; I/O and IRQ present; No Mem Space; Misc Entry Present P:Power info type T:Timing info present IO:I/O port info present IR:Interrupt info present MS:Mem space info type M:Misc info byte(s) present
0C4h	27h	R 0	0	PI 1	AI 0	0	HV 1	LV 1	NV 1	Nominal Voltage Follows NV:Nominal Voltage LV:Mimimum Voltage HB:Maximum Voltage SI:Static Current AI:Average Current PI:Peak Current DI:Power Down Current	Power Parameters for Vcc
0C6h	55h	X 0			ntissa = 5.0			xpon 5h = 1		Vcc Nominal is 5Volts	Vcc Nominal Value
0C8h	4Dh	X 0			ntissa = 4.5			xpon 5h = 1		Vcc Nominal is 4.5 Volts	Vcc Minimum Value
0CAh	5Dh	X 0			ntissa = 5.5			xpon 5h = ^		Vcc Nominal is 5.5Volts	Vcc Maximum Value
0CCh	75h	X 0			ntissa = 8.0			Expon 5h =		Max Average Current over 10 msec is 80 mA	Max Average Current
0CEh	64h	R 0	S 1	E 1		IO A	AddeL 4	ines		Supports both 8 and 16 bit I/O hosts. 4 Address lines and no range so 16 registers and host must do all selection decoding. IO AddrLines:#lines decoded E:Eight bit only hosts supported S:Sixteen bit hosts supported R:Range Follows	TPCE_IO
0D0h	F0h	S 1	P 1	L 1	M 1	V 0	B 0	0	N 0	IRQ Sharing Logic Active in Card Control & Status Register, Pulse and Level Mode Interrupts supported, Recommended IRQ's any of 0 through 15(F) S:Share Logic Active P:Pulse Mode IRQ Supported L:Level Mode IRQ Supported M:Bit Mask of IRQs Present V:Vendor Unique IRQ B:Bus Error IRQ I:IO Check IRQ N:Non-Maskable IRQ	TPCE_IR

Attribute Offset	Data	7	6	5	4	3	2	1	0	Description of Contents	CIS Function
0D2h	FFh	7	6	5	4	3	2	1	0	IRQ Levels to be routed 0 - 15 recommended.	TPCE_IR Mask Extension
		1	1	1	1	1	1	1	1		Byte 1
0D4h	FFh	F 1	E 1	D 1	C 1	B 1	A 1	9	8	Recommended routing to any "normal, maskable" IRQ.	TPCE_IR Mask Extension Byte 2
0D6h	21h	X 0	R 0	P 1	RO 0	A 0		T 1		Power-Down, and Twin Card. T:Twin Cards Allowed A:Audio Supported RO:Read Only Mode P:Power Down Supported R:Reserved X:More Misc Fields Bytes	TPCE_MI
0D8h	1Bh			(CISTI	PL_C	E			Configuration Entry Tuple	Tuple Code
0DAh	06h									Link to next tuple is 6 bytes. Also limits size of this tuple to 8 bytes.	Link to next tuple
0DCh	01h	I	D		Cor	nfigur	ation	Index	(I/O mapped contiguous 16 3.3V configuration	TPCE_INDX
		0	0				1	1			
0DEh	01h	M		1S	IR	Ю	Т		o	P:Power info type	TPCE_FS
		0	(0	0	0	0	·	1		
0E0h	21h	R 0	0	PI 1	AI 0	SI 0	HV 0	LV 0	NV 1	PI:Peak Current NV:Nominal Operation Supply Voltage	Power Parameters for Vcc
0E2h	B5h	X 1			ntissa = 3.0		Е	xpon 5h =		Nominal Operation Supply Voltage = 3.0V	Nominal Operation Supply Voltage
0E4h	1Eh	X 0				1Eh	1			+.30	Nominal Operation Supply Voltage Extension Byte
0E6h	4Dh	X 0			ntissa = 4.5			xpon 5h =		Max Average Current over 10 msec is 45 mA	Max Average Current
0E8h	1Bh			(CISTI	PL_C	Ε			Configuration Entry Tuple	Tuple Code
0EAh	12h									Link to next tuple is 18 bytes. Also limits size of this tuple to 20 bytes.	Link to next tuple
0ECh	C2h	1	D 1		Cor	nfigur	ation 2	Index	<	AT Fixed Disk Primary I/O Address Configuration Configuration Index for this entry is 2. Interface Byte follows this byte. Default Configuration	TPCE_INDX

Attribute Offset	Data	7	6	5	4	3	2	1	0	Description of Contents	CIS Function				
0EEh	41h	W 0	R 1	P 0	B 0	lr		ce Ty	rpe	I/O Interface(1), Bvd's and wProt not used; Ready/-Busy active but Wait not used for memory cycles. B:Battery Volt Detects Used P:Write Protect Used R:Ready/-Busy Used W:Wait Used for Memory Cycles	TPCE_IF				
0F0h	99h	M 1		NS 0	IR 1	10	T 0			Vcc Only Power Description; No Timing; I/O and IRQ present; No Mem Space; Misc Entry present P:Power info type T:Timing info present IO:I/O port info present IR:Interrupt info present MS:Mem space info type M:Misc info byte(s) present	TPCE_FS				
0F2h	27h	R 0	0	PI 1	0	0	HV 1			Nominal Voltage Follows NV:Nominal Voltage LV:Mimimum Voltage HB:Maximum Voltage SI:Static Current Al:Average Current PI:Peak Current DI:Power Down Current	Power Parameters for Vcc				
0F4h	55h	X 0			ntissa = 5.0			xpon 5h =		Vcc Nominal is 5Volts	Vcc Nominal Value				
0F6h	4Dh	X 0			ntissa = 4.5	l		xpon 5h =		Vcc Nominal is 4.5Volts	Vcc Minimum Value				
0F8h	5Dh	X 0			ntissa = 5.5		Ę	Exponent 5h = 1V		5h = 1V		Exponent 5h = 1V		Vcc Nominal is 5.5Volts	Vcc Maximum Value
0FAh	75h	X 0			ntissa = 8.0		Exponent 5h = 10		ent 10	Max Average Current over 10 msec is 80 mA	Max Average Current				
0FCh	EAh	R 1	S 1	1			addeL h = 1			Supports both 8 and 16 bit I/O hosts. 10 Address lines with range so card will respond only to indicated (1F0-1F7, 3F6-3F7) on A9 through A0 for I/O cycles. IO AddrLines:#lines decoded E:Eight bit only hosts supported S:Sixteen bit hosts supported R:Range Follows	TPCE_IO				

Attribute Offset	Data	7	6	5	4	3	2	1	0	Description of Contents	CIS Function				
0FEh	61h		S 1		S 2	N Ranges - 1		1		1		1		Number of Ranges is 2; Size of each address is 2 bytes; Size of each length is 1 byte. AS:Size of Addresses 0:No Address Present 1:1Byte (8 bit) Addresses 2:2Byte (16 bit) Addresses 3:4Byte (32 bit) Addresses LS:Size of length 0:No Lengths Present 1:1Byte (8 bit) Lengths 2:2Byte (16 bit) Lengths 3:4Byte (32 bit) Lengths	I/O Range Format Description
100h	F0h		1s	st I/O	Base	Addr	ess (l	sb)		First I/O Range base is					
102h	01h		1st	t I/O E	Base /	Addre	ess (n	nsb)		1F0h					
104h	07h		1	st I/O	Ran	ge Le	ngth -	- 1		8 bytes total ==> 1F0-1F7h	I/O Length - 1				
106h	F6h	2nd I/O Base Address (Isb)								2nd I/O Range base is					
108h	03h	2nd I/O Base Address (msb)								3F6h					
10Ah	01h	2nd I/O Range Length - 1								2 bytes total ==> 3F6-3F7h	I/O Length - 1				
10Ch	EEh	S 1	P 1	1	M 0	Recommend IRQ Level Eh = 14			IRQ	IRQ Sharing Logic Active in Card Control & Status Register, Pulse and Level Mode Interrupts supported, Recommended IRQ's any of 0 through 15(F) S:Share Logic Active P:Pulse Mode IRQ Supported L:Level Mode IRQ Supported M:Bit Mask of IRQs Present M=0 so bits 3-0 are single level, binary encoded	TPCE_IR				
10Eh	21h	X 0	R 0	P 1	RO 0	A 0				Power-Down, and Twin Card. T:Twin Cards Allowed A:Audio Supported RO:Read Only Mode P:Power Down Supported R:Reserved X:More Misc Fields Bytes	TPCE_MI				
110h	1Bh	CISTPL_CE								Configuration Entry Tuple	Tuple Code				
112h	06h									Link to next tuple is 6 bytes. Also limits size of this tuple to 8 bytes.	Link to next tuple				
114h	02h	0	D Configuration Index 0 2							AT Fixed Disk Primary I/O 3.3V configuration	TPCE_INDX				

Attribute Offset	Data	7	6	5	4	3	2	2 1 0		Description of Contents	CIS Function
116h	01h	М	N	1S	IR	Ю	Т	ı	P	P:Power info type	TPCE_FS
		0	(0	0	0	0		1		
118h	21h	R 0	DI 0	PI 1	AI 0	SI 0	HV 0	LV 0	NV 1	PI:Peak Current NV:Nominal Operation Supply Voltage	Power Parameters for Vcc
11Ah	B5h	X 1			ntissa = 3.0		E	Exponent 5h = 1		Nominal Operation Supply Voltage = 3.0V	Nominal Operation Supply Voltage
11Ch	1Eh	X 0				1Eh	1			+.30	Nominal Operation Supply Voltage Extension Byte
11Eh	4Dh	X 0			ntissa = 4.5			xpon 5h =		Max Average Current over 10 msec is 45mA	Max Average Current
120h	1Bh			(CISTI	PL_C	Ε			Configuration Entry Tuple	Tuple Code
122h	12h		_							Link to next tuple is 18 bytes. Also limits size of this tuple to 20 bytes.	Link to next tuple
124h	C3h	I	D	D Configura			ation	Index	Κ	AT Fixed Disk Secondary I/O	TPCE_INDX
		1	1				3			Address Configuration Configuration Index for this entry is 3. Interface Byte follows this byte. Default Configuration	
126h	41h	W 0	R 1	P 0	B 0	lr	nterface Type		/ре	I/O Interface(1), Bvd's and wProt not used; Ready/-Busy active but Wait not used for memory cycles. B:Battery Volt Detects Used P:Write Protect Used R:Ready/-Busy Used W:Wait Used for Memory Cycles	TPCE_IF
128h	99h	M 1		AS O	IR 1	10 1	T 0			Vcc Only Power Descriptors; No Timing; I/O and IRQ present; No Mem Space; Misc Entry Present. P:Power info type T:Timing info present IO:I/O port info present IR:Interrupt info present MS:Mem space info type M:Misc info byte(s) present	TPCE_FS
12Ah	27h	R 0	O O	PI 1	0 O	0	HV 1	LV NV		Nominal Voltage Follows NV:Nominal Voltage LV:Mimimum Voltage HB:Maximum Voltage SI:Static Current AI:Average Current PI:Peak Current DI:Power Down Current	Power Parameters for Vcc
12Ch	55h	X 0			ntissa = 5.0			xpon 5h =		Vcc Nominal is 5Volts	Vcc Nominal Value
12Eh	4Dh	X 0					xpon 5h =		Vcc Nominal is 4.5Volts	Vcc Minimum Value	

Attribute Offset	Data	7	6	5	4	3	2	1	0	Description of Contents	CIS Function							
130h	5Dh	X 0			ntissa = 5.5		Exponent 5h = 1V			Vcc Nominal is 5.5Volts	Vcc Maximum Value							
132h	75h	X 0			ntissa = 1.0		Exponent 5h = 10										Max Average Current over 10 msec is 80 mA	Max Average Current
134h	EAh	R 1	S 1	E 1		IO AddeLines Ah = 10				Supports both 8 and 16 bit I/O hosts. 10 Address lines with range so card will respond only to indicated (170-177, 376-377) on A9 through A0 for I/O cycles. IO AddrLines:#lines decoded E:Eight bit only hosts supported S:Sixteen bit hosts supported R:Range Follows	TPCE_IO							
136h	61h	1		A 2	0	١	N Ranges–1		-1	Number of Ranges is 2; Size of each address is 2 bytes; Size of each length is 1 byte. AS:Size of Addresses 0:No Address Present 1:1Byte (8 bit) Addresses 2:2Byte (16 bit) Addresses 3:4Byte (32 bit) Addresses LS:Size of length 0:No Lengths Present 1:1Byte (8 bit) Lengths 2:2Byte (16 bit) Lengths 3:4Byte (32 bit) Lengths	I/O Range Format Description							
138h	70h		1:	st I/O	Base	Addre	ess ((Isb)		First I/O Range base is								
13Ah	01h		1s	t I/O E	Base A	Addre	ss (r	msb)		170h								
13Ch	07h		1	st I/C	Ran	ge Lei	ngth	- 1		8 bytes total ==> 170-177h	I/O Length - 1							
13Eh	76h		2r	nd I/O	Base	Addr	ess	(lsb)		2nd I/O Range base is								
140h	03h		2n	d I/O	Base	Addre	ess (ı	msb)		376h								
142h	01h		2	nd I/C) Ran	ge Le	ngth	ı - 1		2 bytes total ==> 376-377h	I/O Length - 1							
144h	EEh	S 1	Level		ecommend IRQ Level		IRQ	IRQ Sharing Logic Active in Card Control & Status Register, Pulse and Level Mode Interrupts supported, Recommended IRQ's any of 0 through 15(F) S:Share Logic Active P:Pulse Mode IRQ Supported L:Level Mode IRQ Supported M:Bit Mask of IRQs Present M=0 so bits 3-0 are single level, binary encoded	TPCE_IR									

Attribute Offset	Data	7	6	5	4	3	2	1	0	Description of Contents	CIS Function	
146h	21h	X 0	R 0	P 1	RO 0	A 0	T 1			Power-Down, and Twin Card. T:Twin Cards Allowed A:Audio Supported RO:Read Only Mode P:Power Down Supported R:Reserved X:More Misc Fields Bytes	TPCE_MI	
148h	1Bh				CIST	PL_C	Ε			Configuration Entry Tuple	Tuple Code	
14Ah	06h									Link to next tuple is 6 bytes. Also limits size of this tuple to 8 bytes.	Link to next tuple	
14Ch	03h	I	D		Cor	ıfigur	ation	Index	(AT Fixed Disk Secondary I/O 3.3V	TPCE_INDX	
		0	0				3			configuration		
14Eh	01h	М	N	1S	IR	10	Т	F)	P:Power info type	TPCE_FS	
		0		0	0	0	0	0 1				
150h	21h	R	DI	PI	Al	SI	HV	<u> </u>		PI:Peak Current NV:Nominal Operation Supply Voltage	Power Parameters for Vcc	
		0	0	1	0	0			1			
152h	B5h	X 1			ntissa = 3.0				Nominal Operation Supply Voltage = 3.0V	Nominal Operation Supply Voltage		
154h	1Eh	X 0		1	Eh			+.30)	Nominal Operation Supply Voltage Extension Byte		
156h	4Dh	X 0			ntissa = 4.5			xpon 5h =		Max Average Current over 10 msec is 45mA	Max Average Current	
158h	1Bh				CIST	PL_C	Ε			Configuration Entry Tuple	Tuple Code	
15Ah	04h									Link to next tuple is 4 bytes.	Link to next tuple	
15Ch	07h	1 0	D Configuration Index					n Inde	ΣX	AT Fixed Disk Secondary I/O 3.3V configuration	TPCE_INDX	
15Eh	00h	М		MS	IF	1	0	0 T P		P:Power info type	TPCE_FS	
		0		0	0		0 0 0		0			
160h	028h		<u> </u>		1	<u> </u>				SanDisk Code	Reserved	
162h	0D3h									SanDisk Code	Reserved	
164h	014h	CISTPL_NO_LINK								Prevent Scan of Common Memory	Tuple Code	
166h	000h			No	Bytes	Follo	wing			Link Length is 0 Bytes	Link to next tuple	
168h	0FFh	End of Tuple Chain								End of CIS	Tuple Code	



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Appendix A. Ordering Information

To order SanDisk products directly from SanDisk, call 408-542-0595.

CompactFlash Memory Card Evaluation Kit

The CompactFlash Memory Card Evaluation Kit (Model SDCFEV-01) permits designers to quickly and easily evaluate the CompactFlash Card.

The CompactFlash Memory Card Evaluation Kit (Model SDCFEV-01) includes the following items:

- Hardware
 - Evaluation adapter board
 - CompactFlash Memory Card
 - CF Adapter
 - Card extender
 - Adapter board
 - 50 position surface mount header with co-planar tails
 - 50 position straddle mount header for CF Adapter
- Software
 - FlashDisk Driver and Utilities 3.5-inch diskette
- Documentation
 - Read Me First flyer
 - CompactFlash Evaluation Kit User's Guide
 - Applications Note: Differences between PC Card ATA and CF

Model SDCFEV-01

To order, or for more information call:

408-542-0595.

System Software, Card Reader/Writers and Connectors Compatible with SanDisk CompactFlash Memory Cards

Table A-1. System Software with SanDisk CompactFlash Memory Card Support

Vendor	Product Name	Telephone Number
AMI	AMICARDZ	770-263-8181
Award/VMI	Cardware	415-968-4433
Databook	Card Talk for Databook Chip	508-762-9779
Phoenix	Phoenix Card Manager Plus	714-440-8000
SystemSoft	Card Soft	508-651-0088
Vadem	Socket Services for VG365, VG465, VG468	408-467-2100

Table A-2 lists PC card reader/writers that are compatible with the SanDisk CompactFlash Memory Card when used with a passive Type II adapter. These reader/writers can be installed in desktop PCs to enable the CompactFlash Memory Card to be used in those systems. The CompactFlash Memory Card will operate in any of these reader/writers when used with a passive Type II adapter.

NOTE: The SanDisk ImageMate, listed below, does not require use of a Type II adapter.

Table A-2. Card Readers/Writers Compatible with SanDisk CompactFlash Memory Cards

Vendor	Country	Telephone/FAX Number	Product Model	Product Type
Adtron	United States	602-926-9324 FAX 602-926-9359 http://www.adtron.com	SDDA	Adapter for direct IDE-mode operation; 16-bit data interface, BIOS compatible (no drivers); 3.5- or 2.5-inch mount; can replace laptop hard drives.
			SDDB	IDE or ISA connected 8-bit drive; front access.
			SDDC	Industry standard ISA dual-slot adapter, rear entry, cabled to front entry or 100% internal access.
			SDDL	External LPT port drive.
			SDDM	8-bit PC/104 drive.
			SDDP	16-bit PC/104 industry standard adapter.
			SDDR	External RS-232 drive.
			SDDS	Dual-slot SCSI bus drive; ATA card appears as removable disk device; compatible with PC, Macintosh and most workstations.

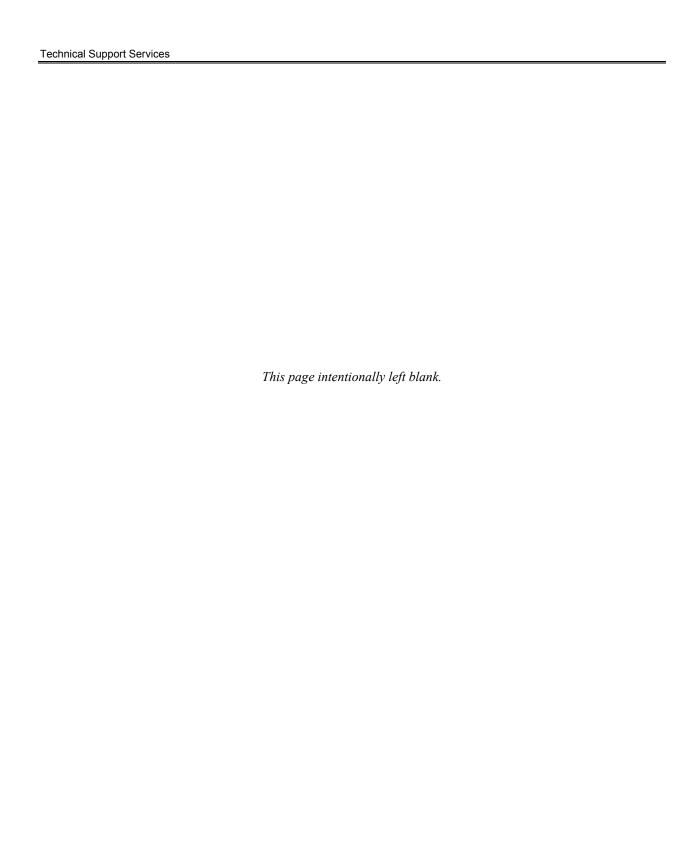
Appendix B. Technical Support Services

Direct SanDisk Technical Support

Call SanDisk Applications Engineering at 408-542-0405 for technical support.

SanDisk Worldwide Web Site

Internet users can obtain technical support and product information along with SanDisk news and much more from the SanDisk Worldwide Web Site, 24 hours a day, seven days a week. The SanDisk Worldwide Web Site is frequently updated. Visit this site often to obtain the most up-to-date information on SanDisk products and applications. The SanDisk Web Site URL is http://www.sandisk.com.



Appendix C. SanDisk Worldwide Sales Offices

SanDisk Corporate Headquarters

140 Caspian Court Sunnyvale, CA 94089 Tel: 408-542-0500 Fax: 408-542-0503

http://www.sandisk.com

U.S. Industrial/OEM Sales

Northwest USA

2241 Fremont Dr., Suite B

Havasu City, AZ 86406 Tel: 928-505-4258 Fax: 928-505-4259

Southwest USA and Mexico

140 Caspian Court Sunnyvale, CA 94089 Tel: 408-542-0730

Fax: 408-542-0410

North Central USA and **South America**

134 Cherry Creek Circle, Suite 150

Winter Srings, FL 32708 Tel: 407-366-6490 Fax: 407-366-5495

Northeastern USA and Canada

620 Herndon Pkwy. Suite 200

Herndon, VA 22070 Tel: 703-481-9828 Fax: 703-437-9215

International Industrial/OEM Sales

Europe

SanDisk GmbH Karlsruher Str. 2C

D-30519 Hannover, Germany

Tel: 49-511-875-9131 Fax: 49-511-875-9187

Northern Europe

Videroegatan 3 B S-16440 Kista, Sweden Tel: 46-08-75084-63 Fax: 46-08-75084-26

Central and Southern Europe

Rudolf-Diesel-Str. 3 40822 Mettmann, Germany Tel: 49-210-495-3433 Fax: 49-210-495-3434

Japan

8F Nisso Bldg. 15 2-17-19 Shin-Yokohama, Kohoku-ku Yokohama 222-0033,

Japan

Tel: 81-45-474-0181 Fax: 81-45-474-0371

Asia/Pacific Rim

Suite 3402, Tower I, Lippo Center 89 Queensway

Admiralty, Hong Kong Tel: 852-2712-0501 Fax: 852-2712-9385

To order SanDisk products directly from SanDisk, call 408-542-0595.



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Appendix D. Limited Warranty

I. WARRANTY STATEMENT

SanDisk warrants its products to be free of any defects in materials or workmanship that would prevent them from functioning properly for one year from the date of purchase. This express warranty is extended by SanDisk Corporation to its customers.

II. GENERAL PROVISIONS

This warranty sets forth the full extent of SanDisk's responsibilities regarding the SanDisk CompactFlash. In satisfaction of its obligations hereunder, SanDisk, at its sole option, will either repair, replace or refund the purchase price of the product.

NOTWITHSTANDING ANYTHING ELSE IN THIS LIMITED WARRANTY OR OTHERWISE, THE EXPRESS WARRANTIES AND OBLIGATIONS OF SELLER AS SET FORTH IN THIS LIMITED WARRANTY, ARE IN LIEU OF, AND BUYER EXPRESSLY WAIVES ALL OTHER OBLIGATIONS, GUARANTIES AND WARRANTIES OF ANY KIND, WHETHER EXPRESS OR IMPLIED, INCLUDING WITHOUT LIMITATION, ANY IMPLIED WARRANTY OF MERCHANTABILITY OR FITNESS FOR A PARTICULAR PURPOSE OR INFRINGEMENT, TOGETHER WITH ANY LIABILITY OF SELLER UNDER ANY CONTRACT, NEGLIGENCE, STRICT LIABILITY OR OTHER LEGAL OR EQUITABLE THEORY FOR LOSS OF USE, REVENUE, OR PROFIT OR OTHER INCIDENTAL OR CONSEQUENTIAL DAMAGES, INCLUDING WITHOUT LIMITATION PHYSICAL INJURY OR DEATH, PROPERTY DAMAGE, LOST DATA, OR COSTS OF PROCUREMENT OF SUBSTITUTE GOODS, TECHNOLOGY OR SERVICES. IN NO EVENT SHALL THE SELLER BE LIABLE FOR DAMAGES IN EXCESS OF THE PURCHASE PRICE OF THE PRODUCT, ARISING OUT OF THE USE OR INABILITY TO USE SUCH PRODUCT, TO THE FULL EXTENT SUCH MAY BE DISCLAIMED BY LAW.

SanDisk's products are not warranted to operate without failure.

III. WHAT THIS WARRANTY COVERS

For products found to be defective within one year of purchase, SanDisk will have the option of repairing or replacing the defective product, if the following conditions are met:

- A. The defective product is returned to SanDisk for failure analysis as soon as possible after the failure occurs.
- B. An incident card filled out by the user, explaining the conditions of usage and the nature of the failure, accompanies each returned defective product.
- C. No evidence is found of abuse or operation of products not in accordance with the published specifications, or of exceeding storage or maximum ratings or operating conditions.

All failing products returned to SanDisk under the provisions of this limited warranty shall be tested to the product's functional and performance specifications. Upon confirmation of failure, each product will be analyzed, by whatever means necessary, to determine the root cause of failure. If the root cause of failure is found to be not covered by the above provisions, then the product will be returned to the customer with a report indicating why the failure was not covered under the warranty.

This warranty does not cover defects, malfunctions, performance failures or damages to the unit resulting from use in other than its normal and customary manner, misuse, accident or neglect; or improper alterations or repairs.

SanDisk reserves the right to repair or replace, at its discretion, any product returned by its customers, even if such product is not covered under warranty, but is under no obligation to do so.

SanDisk may, at its discretion, ship repaired or rebuilt products identified in the same way as new products, provided such cards meet or exceed the same published specifications as new products. Concurrently, SanDisk also reserves the right to market any products, whether new, repaired, or rebuilt, under different specifications and product designations if such products do not meet the original product's specifications.

IV. RECEIVING WARRANTY SERVICE

According to SanDisk's warranty procedure, defective product should be returned only with prior authorization from SanDisk Corporation. Please contact SanDisk's Customer Service department at 408-542-0595 with the following information: product model number and description, nature of defect, conditions of use, proof of purchase and purchase date. If approved, SanDisk will issue a Return Material Authorization or Product Repair Authorization number. Ship the defective product to:

SanDisk Corporation Attn: RMA Returns (Reference RMA or PRA #) 140 Caspian Court Sunnyvale, CA 94089

V. STATE LAW RIGHTS

SOME STATES DO NOT ALLOW THE EXCLUSION OR LIMITATION OF INCIDENTAL OR CONSEQUENTIAL DAMAGES, OR LIMITATION ON HOW LONG AN IMPLIED WARRANTY LASTS, SO THE ABOVE LIMITATIONS OR EXCLUSIONS MAY NOT APPLY TO YOU. This warranty gives you specific rights and you may also have other rights that vary from state to state.

Appendix E. Disclaimer of Liability

San Disk Corporation Policy

SanDisk Corporation general policy does not recommend the use of its products in life support applications wherein a failure or malfunction of the product may directly threaten life or injury. Accordingly, in any use of products in life support systems or other applications where failure could cause damage, injury or loss of life, the products should only be incorporated in systems designed with appropriate redundancy, fault tolerant or back-up features.

SanDisk shall not be liable for any loss, injury or damage caused by use of the Products in any of the following applications:

- Special applications such as military related equipment, nuclear reactor control, and aerospace
- Control devices for automotive vehicles, train, ship and traffic equipment
- Safety system for disaster prevention and crime prevention
- Medical related equipment including medical measurement device